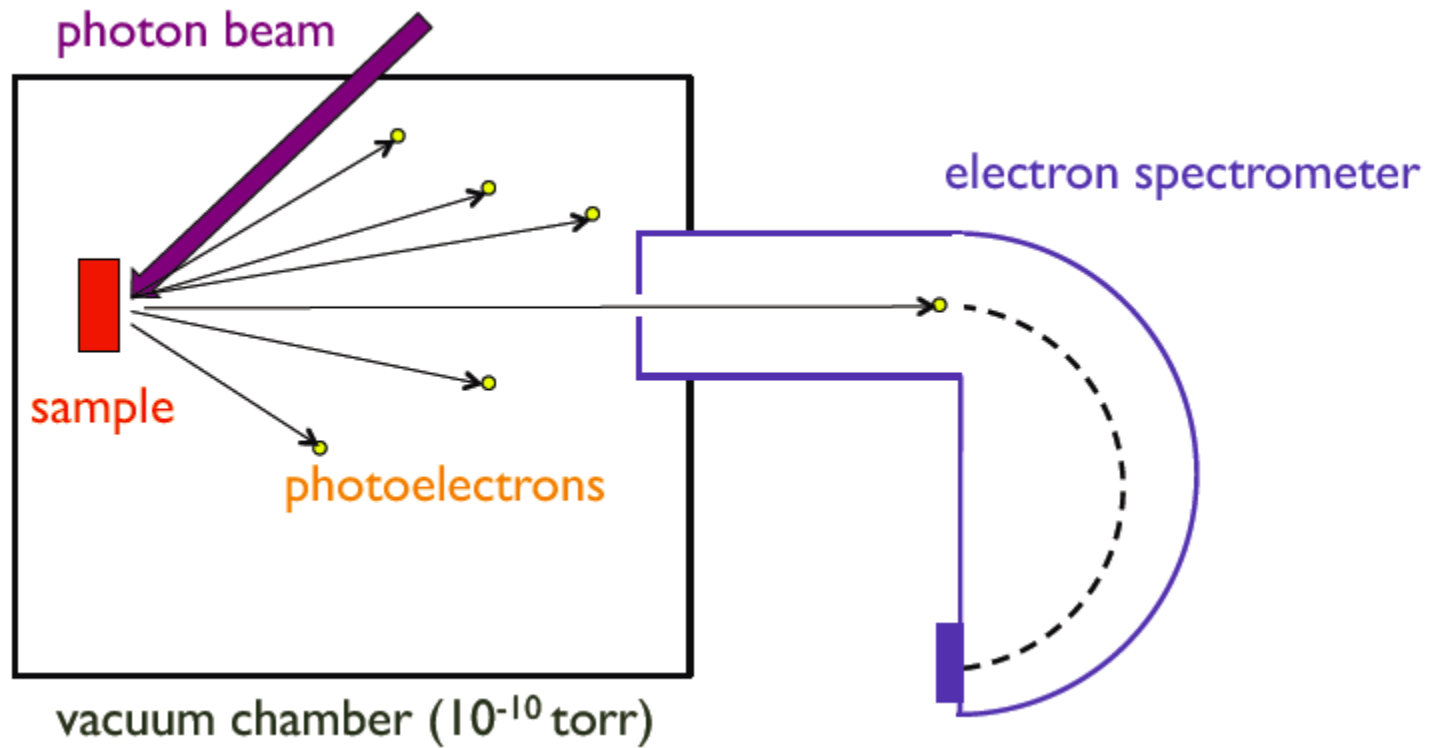


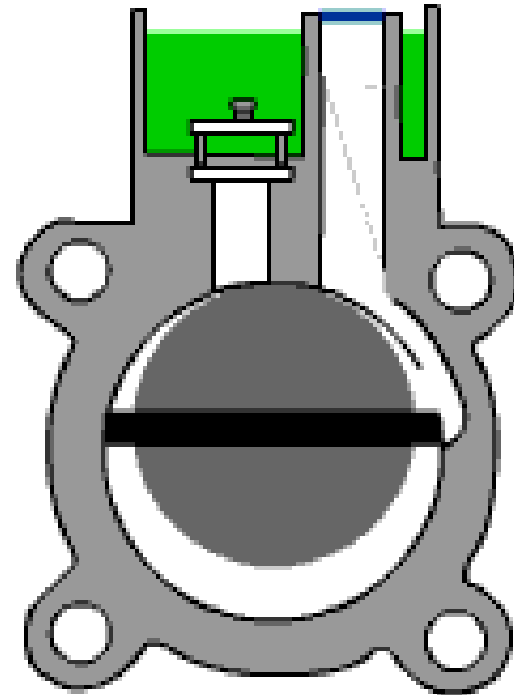
实验站真空系统

Vacuum ! !



Methods for Vacuum Generation: 1

- **Positive displacement:** use a mechanism to repeatedly expand a cavity, allow gases to flow in from the chamber, seal off the cavity, and exhaust it to the atmosphere (rotary vane, scroll pump, roots blower)



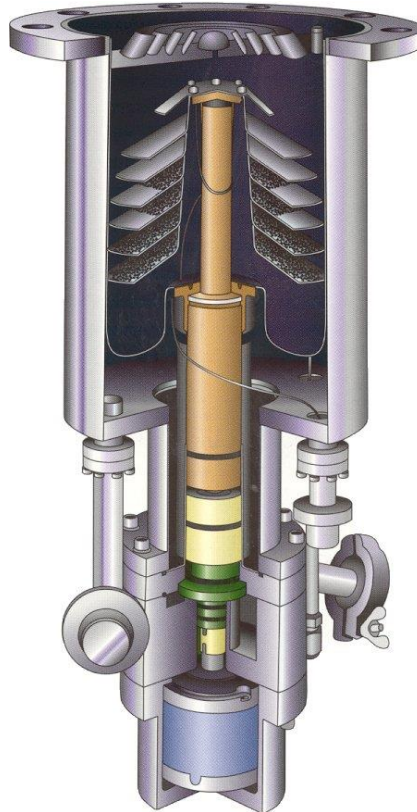
Methods for Vacuum Generation: 2

- **Momentum transfer:** use high speed jets of fluid or rotating blades to knock gaseous molecules out of the chamber (diffusion, turbomolecular)

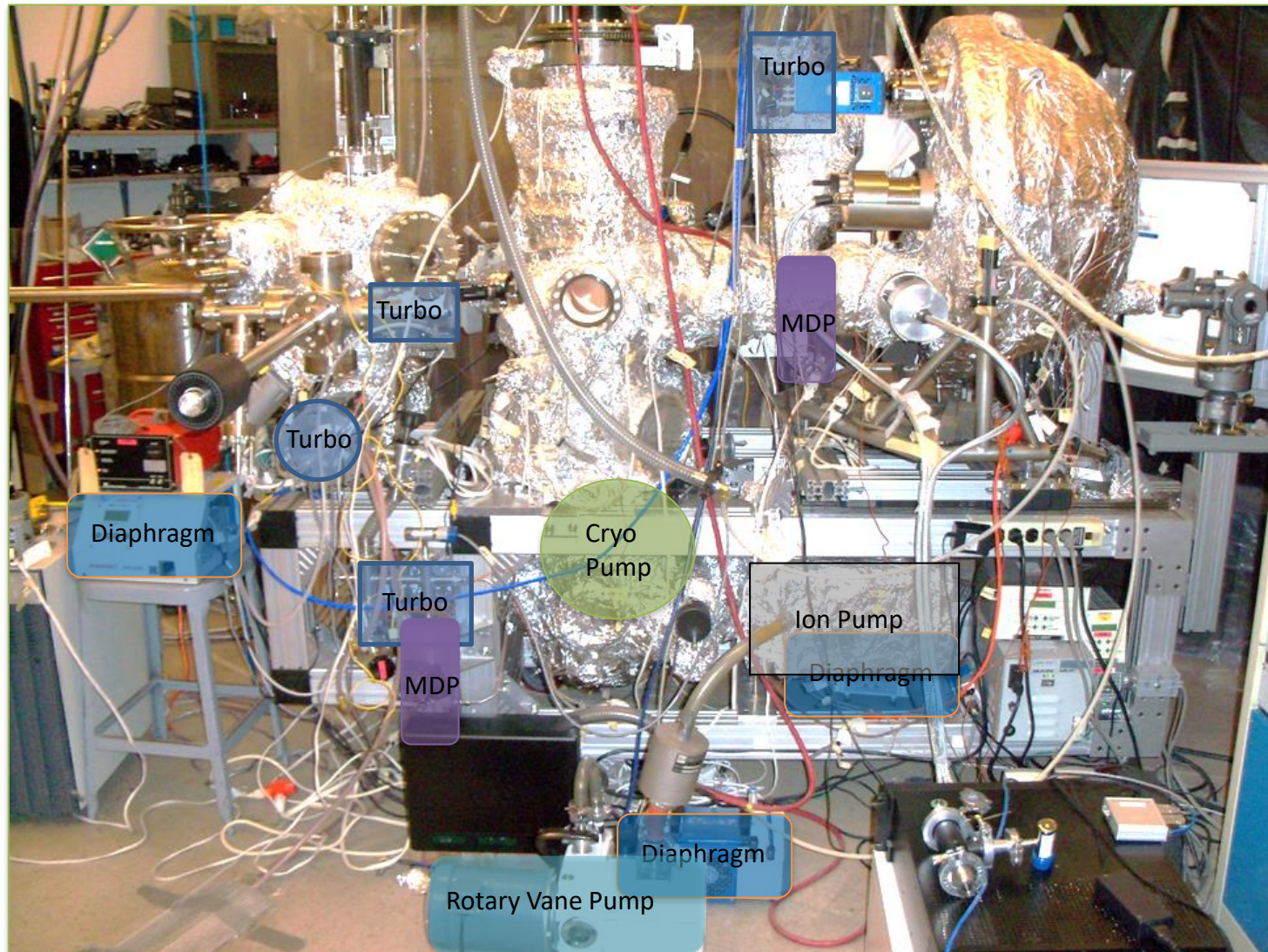


Methods for Vacuum Generation: 3

- **Entrapment:** capture gases in a solid or absorbed state (cryopumps, getters, ion pumps)

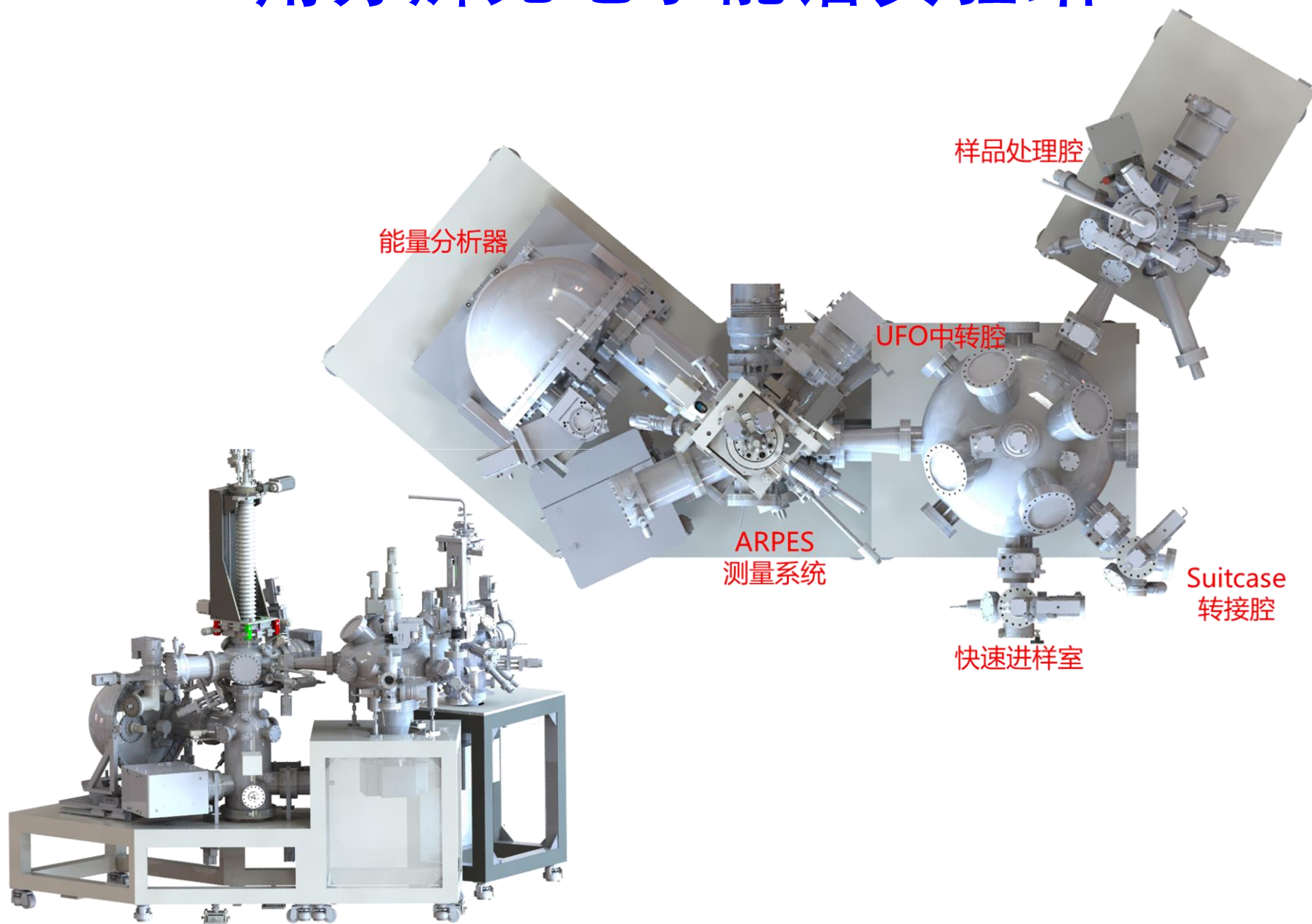


角分辨光电子能谱实验站



Probability of everything working at once $\sim (98\%)^{30} = 55\%$

角分辨光电子能谱实验站



角分辨光电子能谱实验站

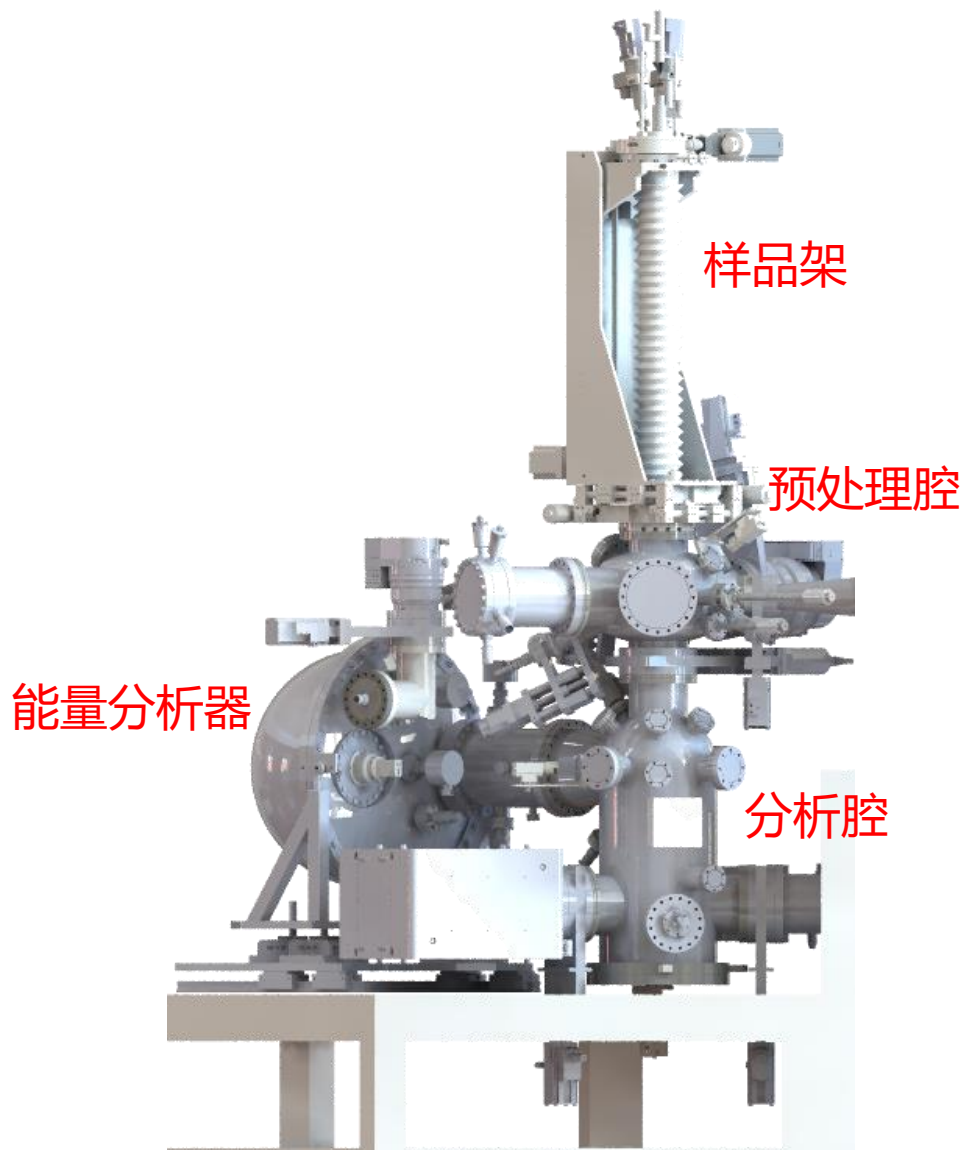
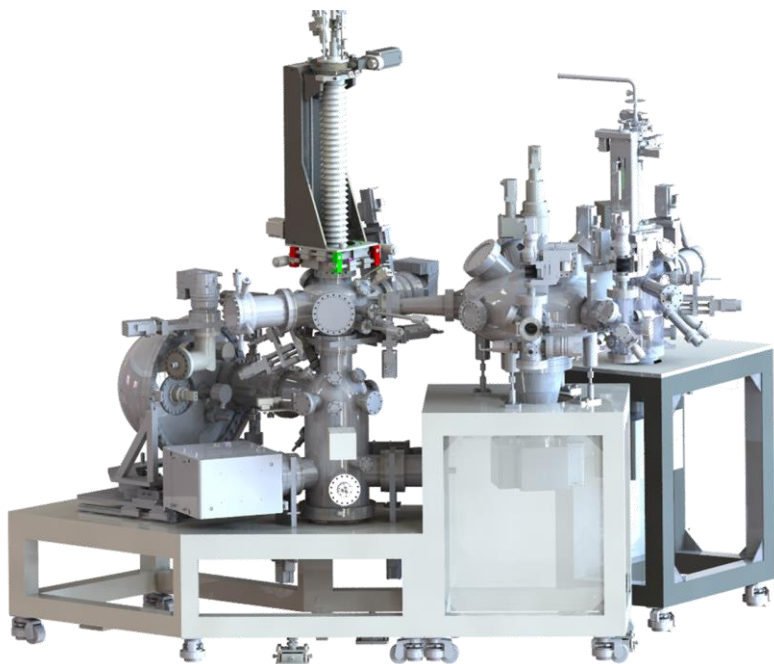
- 上下腔构造

保护主腔超高真空

易于维护

上腔集成多种功能

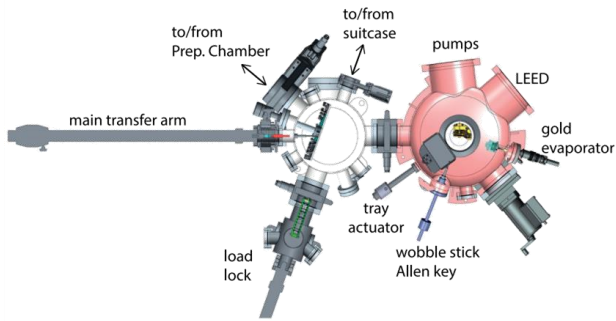
配备LEED、碱金属蒸发源



角分辨光电子能谱实验站

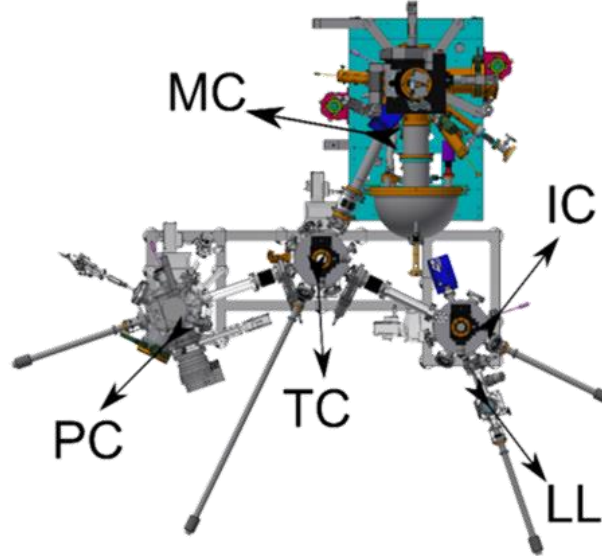
中转传样的选择

Diamond I05 HR-ARPES



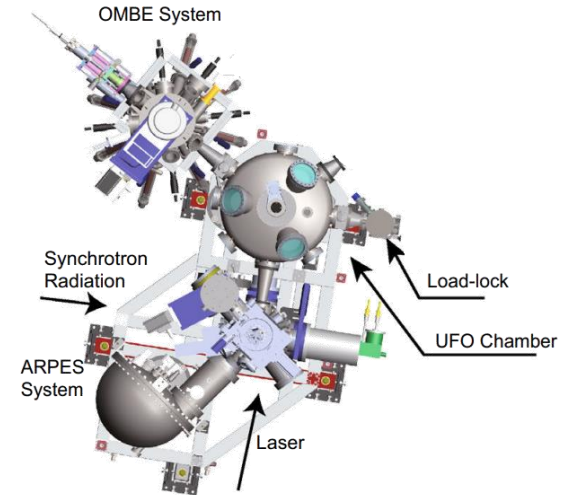
- 传样距离短
- 功能扩展受限

LNLS SAPE



- 传样杆过长/操作不便
- 布局不紧凑
- 功能扩展受限

SSRF ME²



- UFO传样距离合适
- 操作便利
- 布局紧凑
- 功能扩展强

在真空方面需要注意的问题

不能使用的材料:

- S, Pb, Zn, Cd, Hg
- 润滑油
- 有机物 (指纹)
- 不能承受200°C烘烤的材料

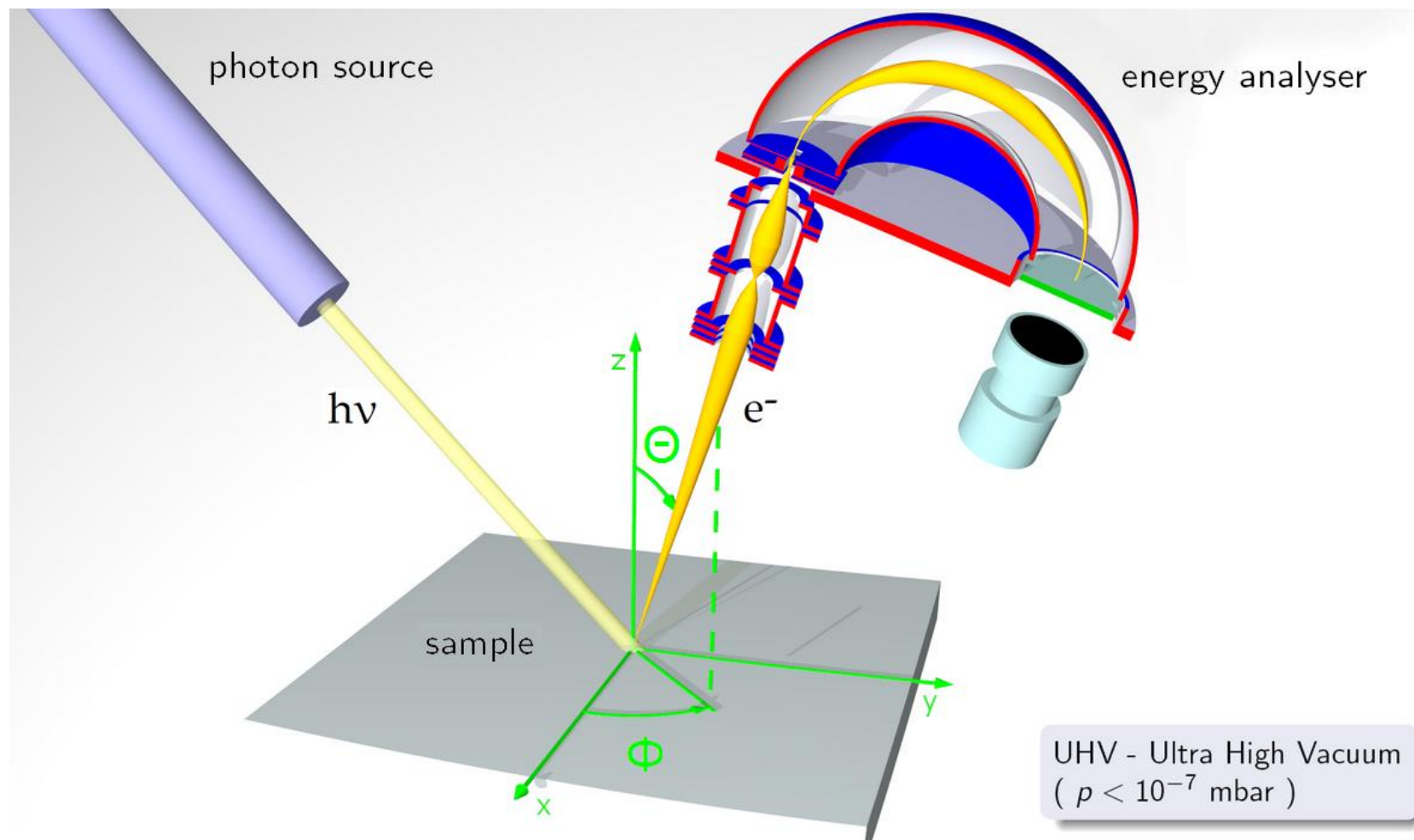
虚漏:

- 腔体焊接问题, 未通气的孔洞

磁性材料(ARPES):

- 大多数不锈钢、铁、镍等

实验中的问题



实验中的问题

样品荷电问题 – 绝缘体、弱绝缘体、 样品制备问题

1. 改变光通量，观察特征峰或费米能级的移动
2. 提高样品温度
3. 用电子枪补偿电子

实验中的问题

Space charge effect – 高光通量

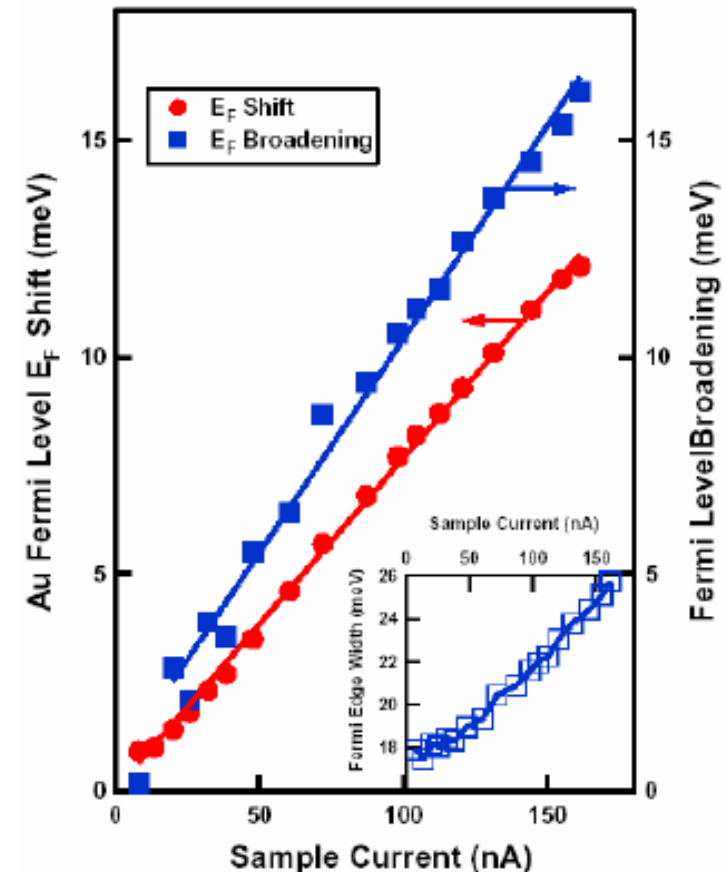
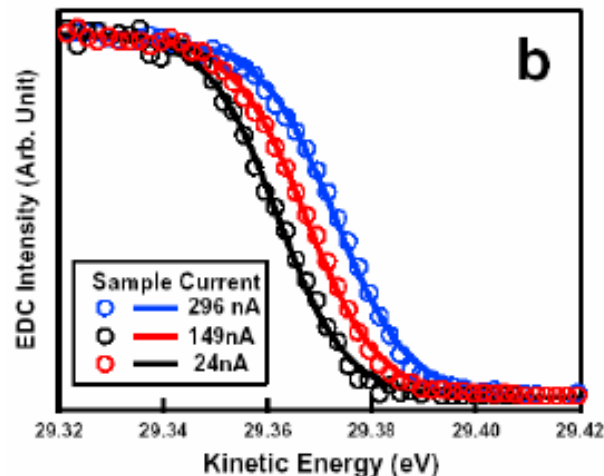
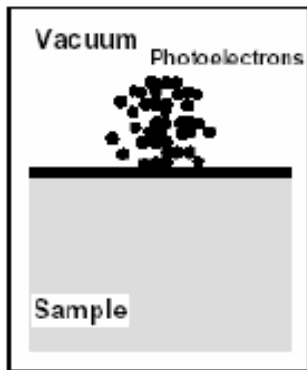
1. 使谱峰变宽、移动
2. 在高光强、高分辨率时出现
3. 调整光强度
3. 让光斑弥散开

Space charge effect

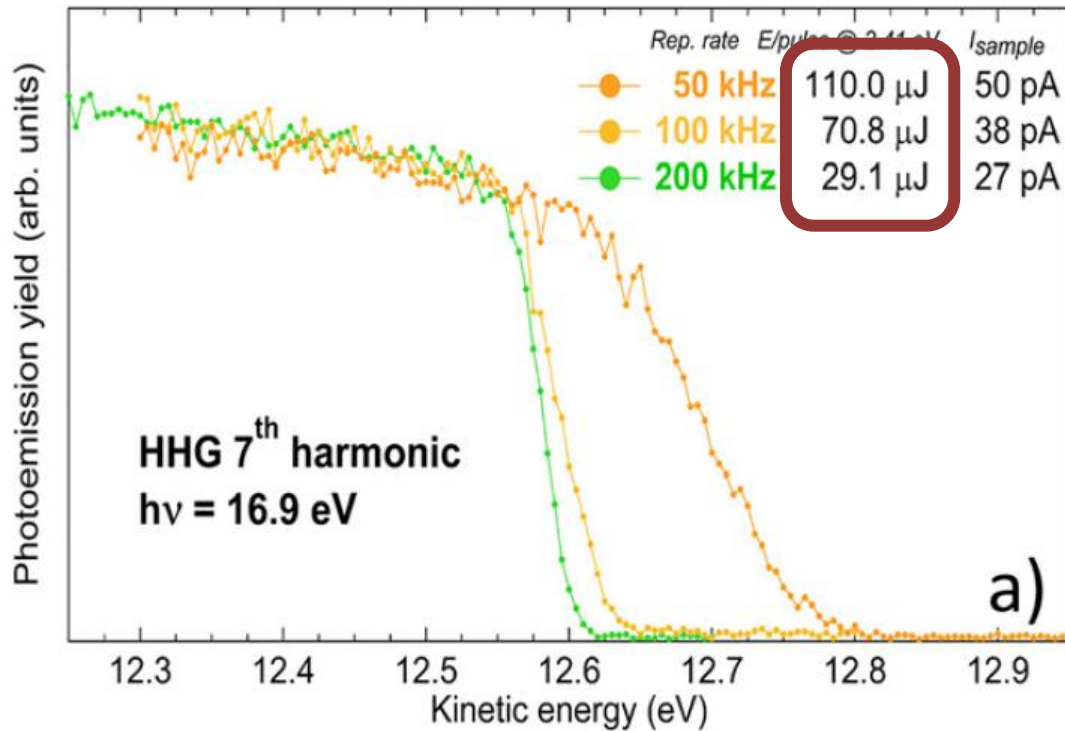
Space charge effect and mirror charge effect in photoemission spectroscopy

X.J. Zhou^{a,b,*}, B. Wannberg^c, W.L. Yang^{a,b}, V. Brouet^{a,b}, Z. Sun^d, J.F. Douglas^d, D. Dessau^d, Z. Hussain^b, Z.-X. Shen^a

From ALS undulator beamline 10.0.1



Space charge的影响



Struct. Dyn. 7, 014303 (2020)

能量尺度上:

- 展宽
- 移动

Space charge的影响

Space charge的影响在三代光源上已经比较明显，在FEL上对数据的影响更显著：

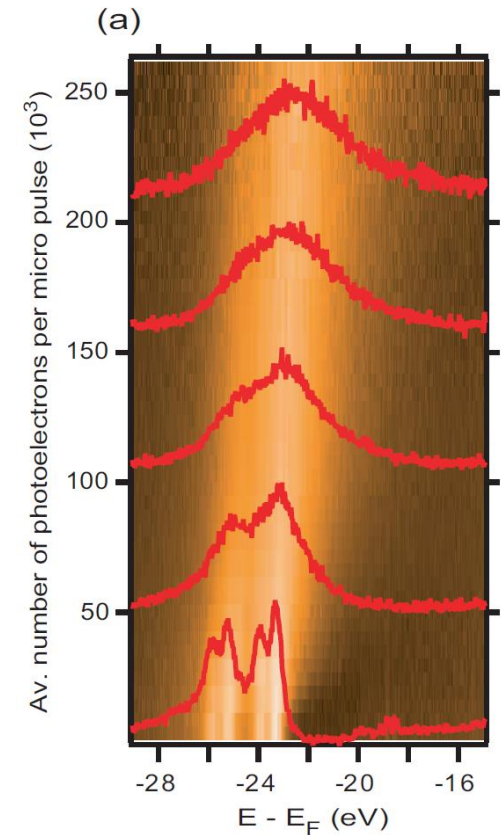
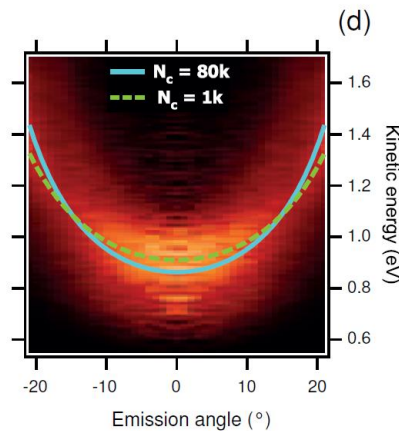
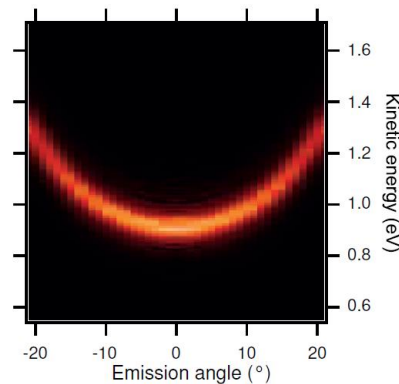
- 数据质量——谱线展宽
- 数据可靠性——能量尺度上移动
- 非线性效应——色散不准确

Photoelectron Spectroscopy at a Free-Electron Laser:
Investigation of Space-Charge Effects in
Angle-Resolved and Core-Level Spectroscopy
and
Realization of a Time-Resolved Core-Level
Photoemission Experiment

Dissertation
zur Erlangung des Doktorgrades
der Mathematisch-Naturwissenschaftlichen Fakultät
der Christian-Albrechts-Universität
zu Kiel

vorgelegt von
Martin Marczyński-Bühlow

Kiel 2011



实验中的问题

样品变性

1. 气体物理吸附、化学吸附，升温可能有帮助
2. 氧原子离开样品表面，低温有帮助
3. 光损伤，用低能光子、低光通量
4. 快速测量、在多个样品测不同信息

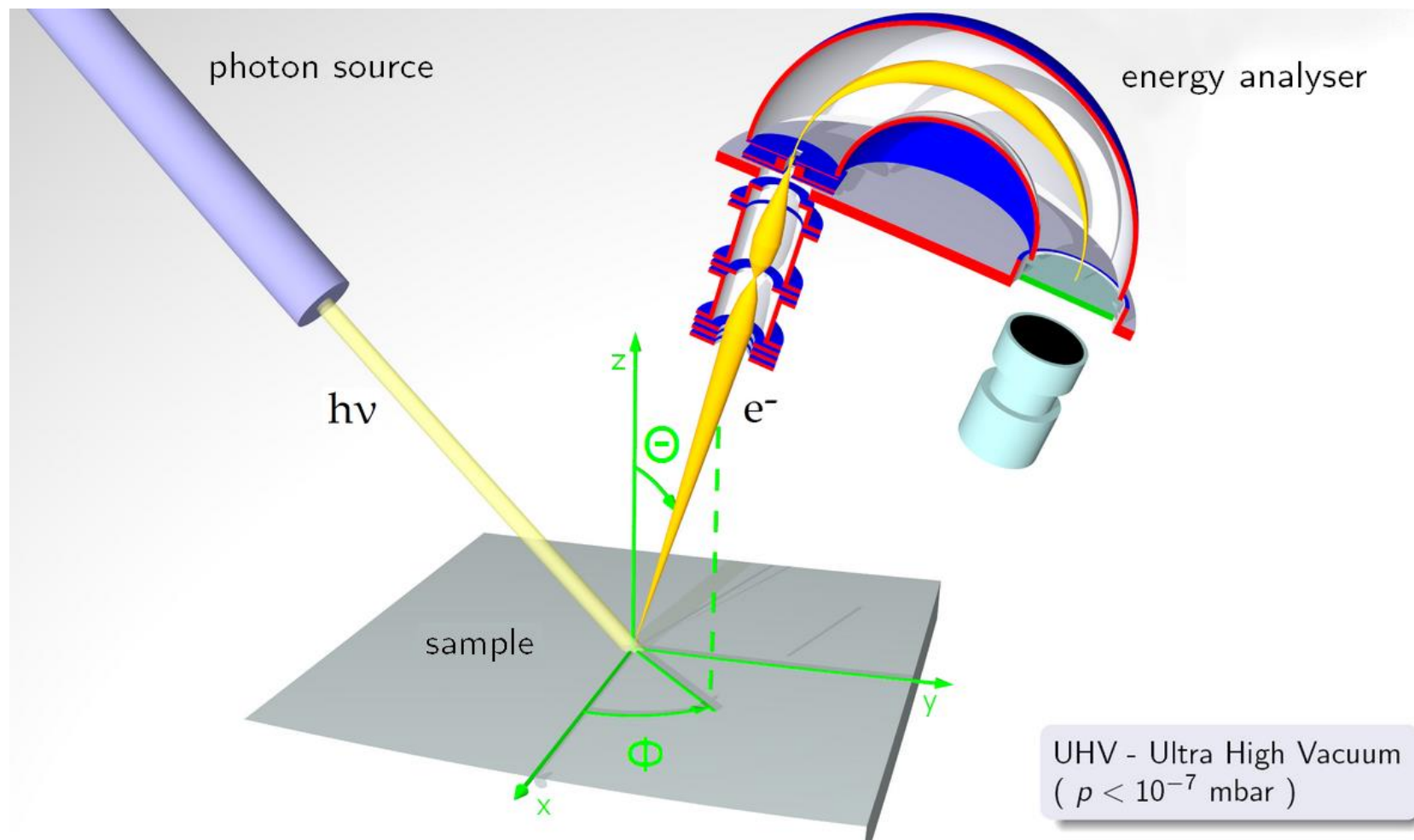
实验中的问题

表面质量

1. 对角分辨实验特别重要
2. 缺陷、杂质、台阶
3. 不同区域功函数问题

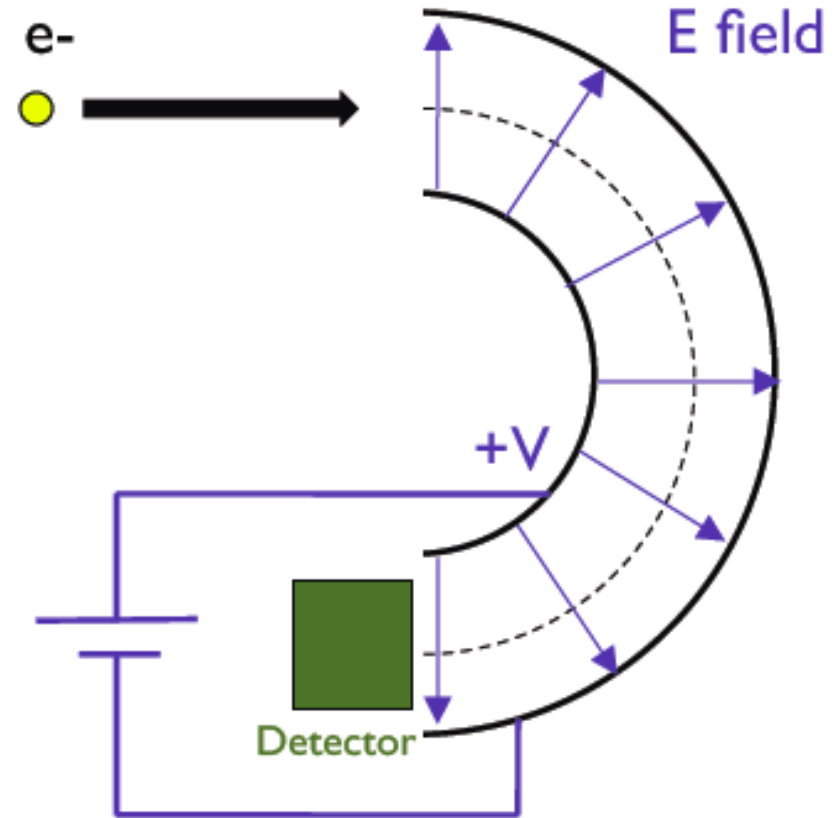
能量分析器

能量分析器

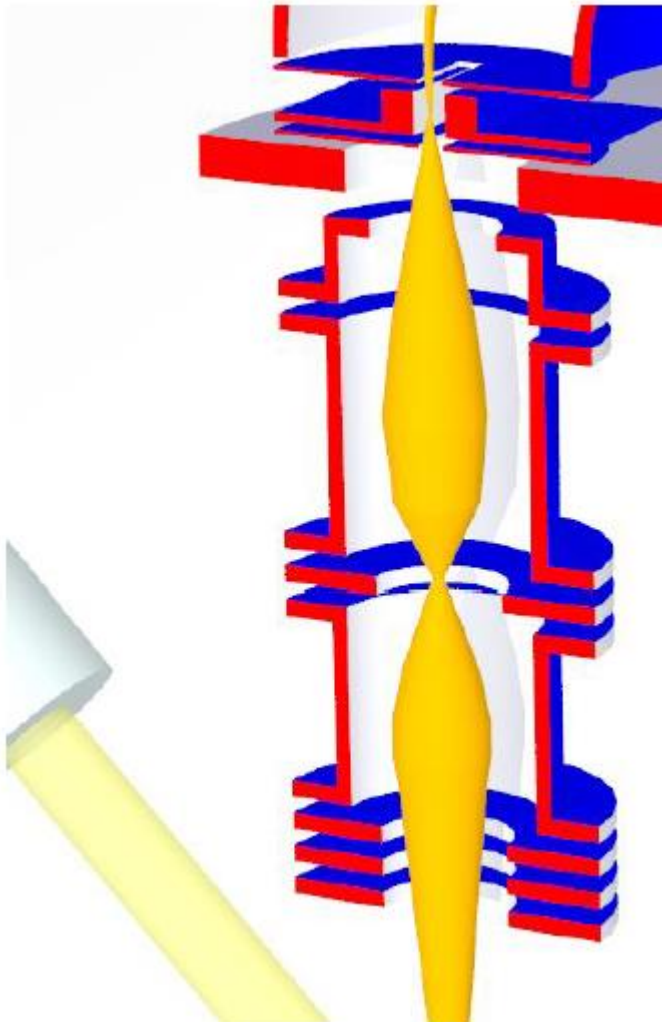


能量分析器

- typical energy resolution ~ 0.1 to 0.01 eV.
Best systems are ~ 0.001 eV.
- most electron analyzers operate using electrostatic optics (magnetic fields harder to control)
- detectors are typically channel plates (electron multipliers) with a CCD or current pulse output
- detecting & manipulating electrons is relatively easy



Retarding and focusing

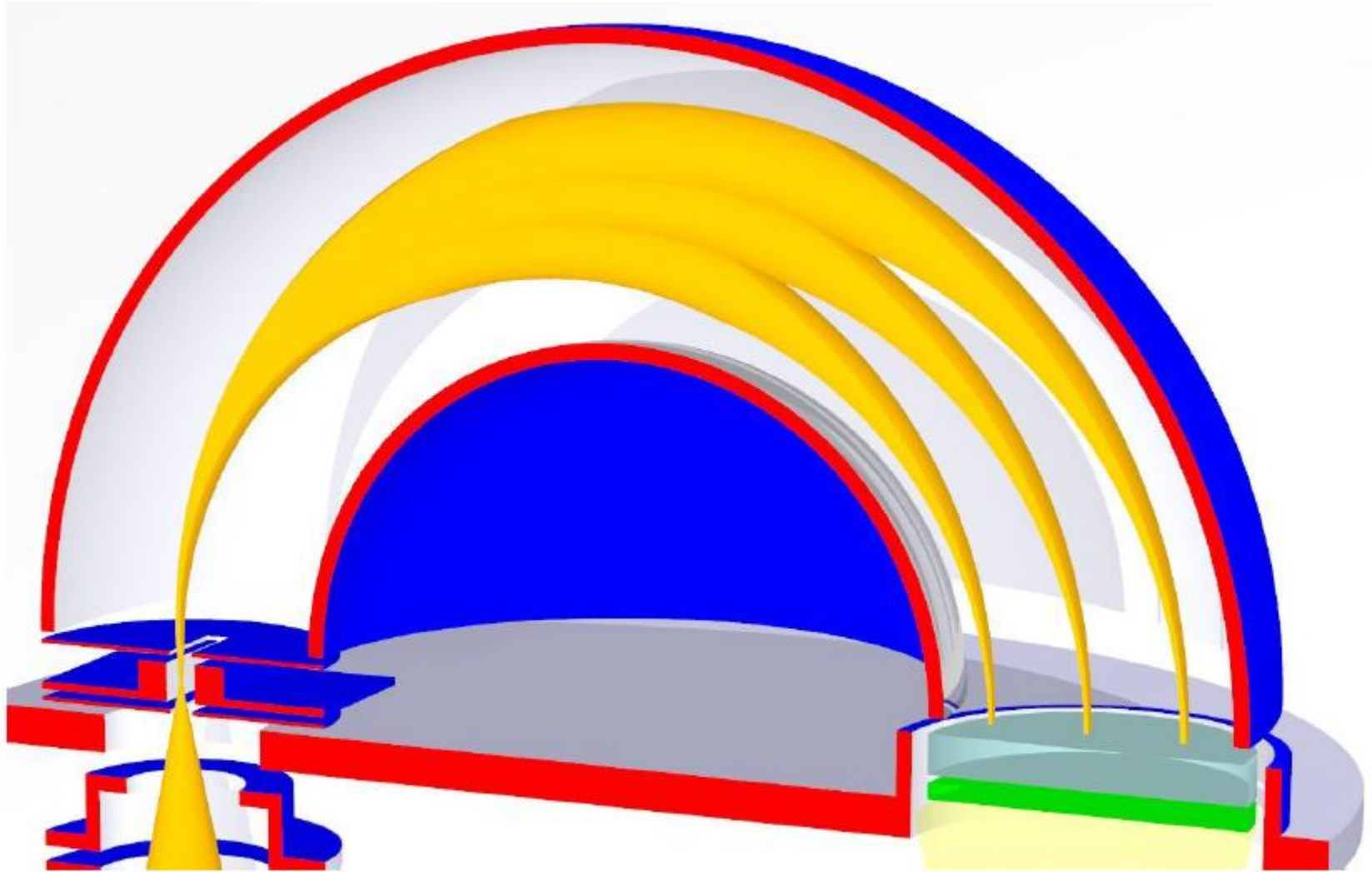


Preretarding stage

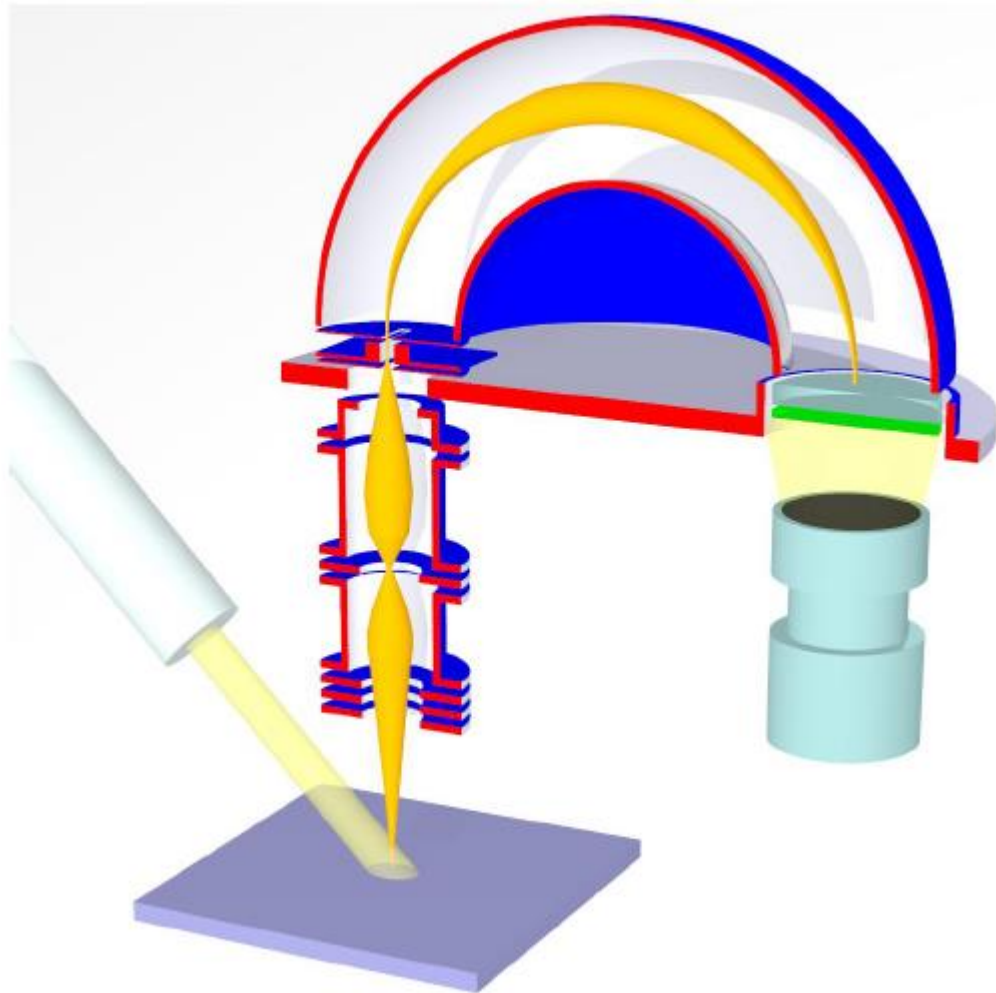
Usually a preretarding stage is used prior to the energy analysis. Electrons enter the analyser with a specified pass energy. One can decelerate (or accelerate) electrons (almost) without changing their absolute energy spread. Measured kinetic energy:

$$E_{kin,A} = E_{pass} - U_{ret}$$

能量分辨



能量分辨率



Potentials on hemispheres

For transmission of electrons with initial energy E_0 along a path with $R_0 = (R_{in} + R_{out})/2$ the potential has to be

$$V_{out} = E_0[3 - 2(R_0/R_{out})]$$

$$V_{in} = E_0[3 - 2(R_0/R_{in})]$$

Resolution

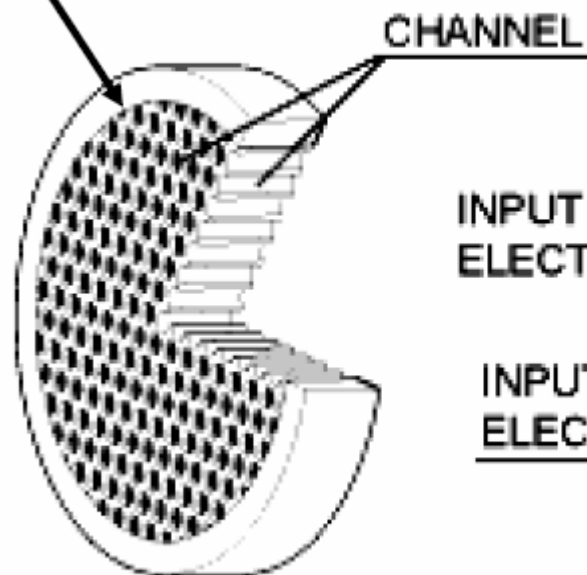
$$\frac{\Delta E}{E_{pass}} = \frac{w}{2R_0} + \alpha^2$$

w width entrance slit

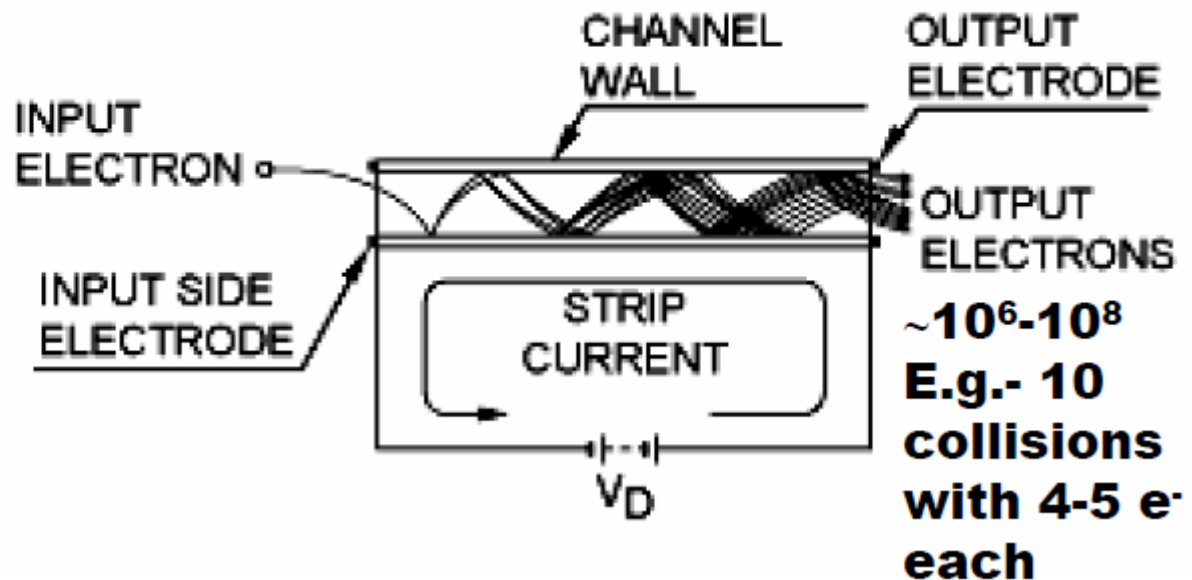
α acceptance angle

Microchannel Plate

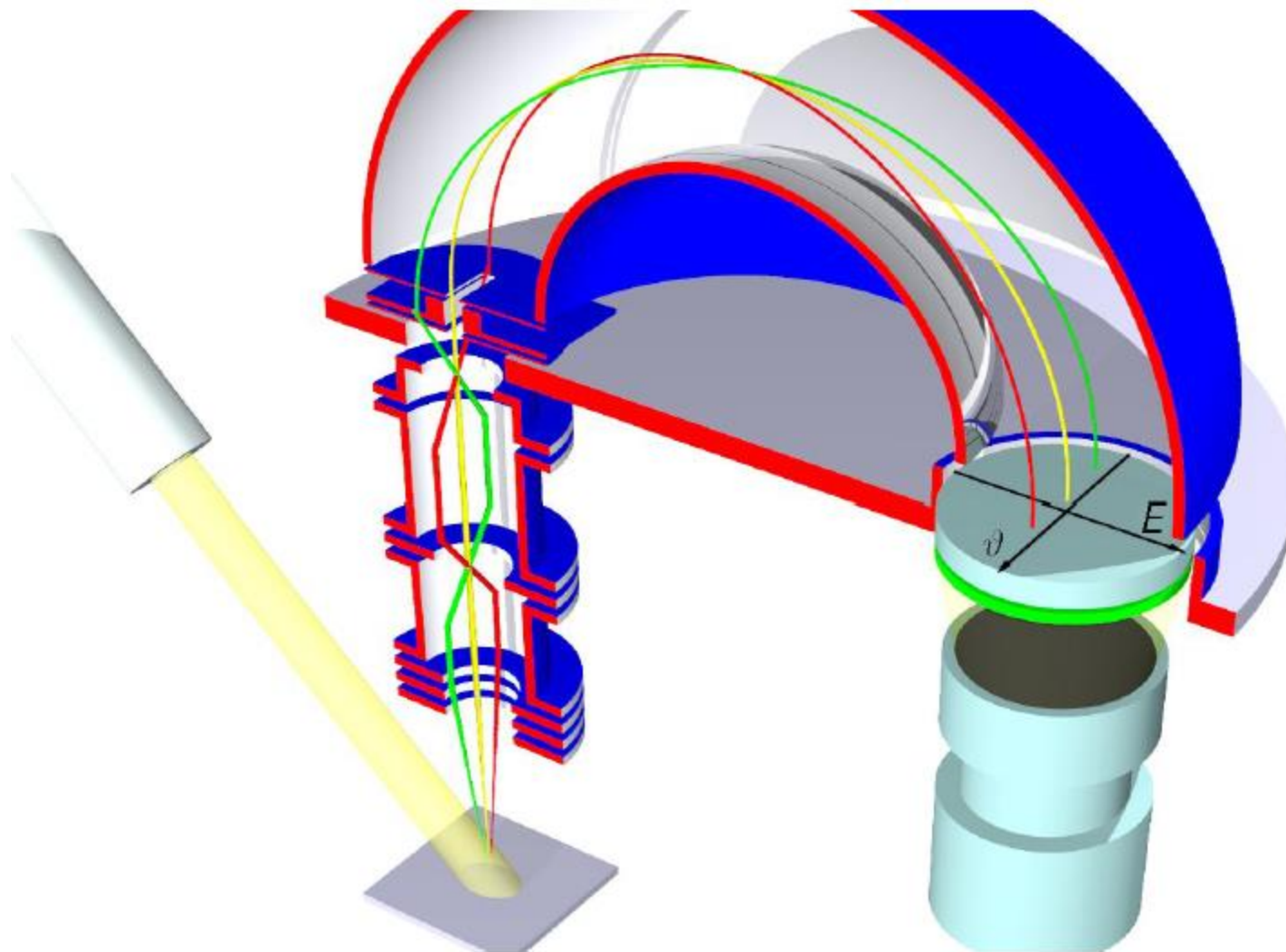
**Diam.
Down to 5
microns**



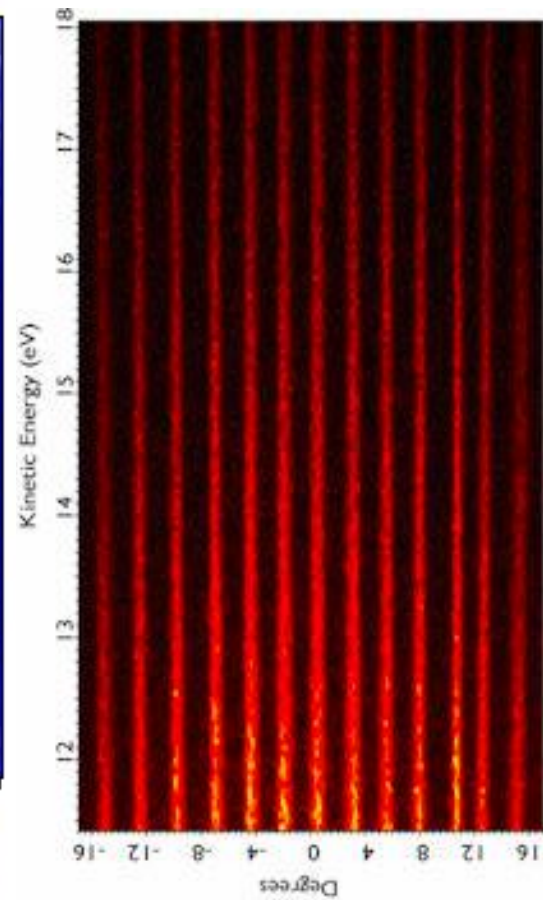
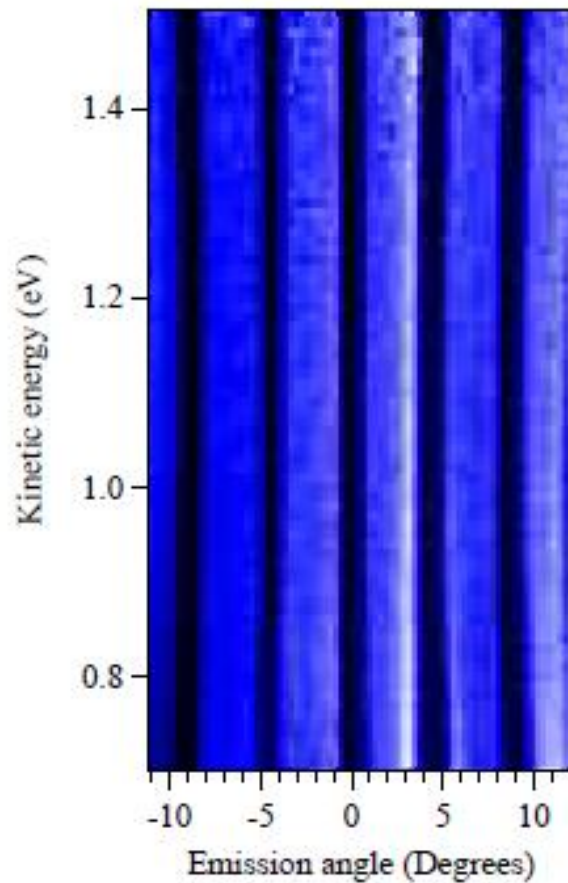
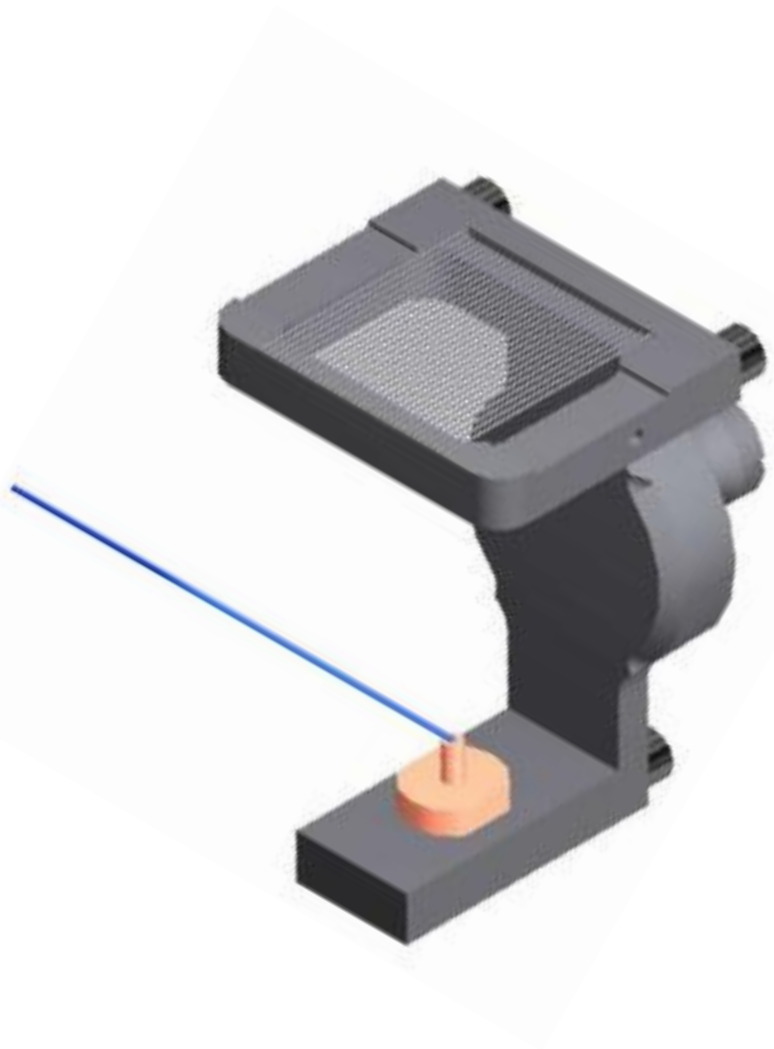
Pb-DOPED GLASS



角度分辨



角度分辨率测量



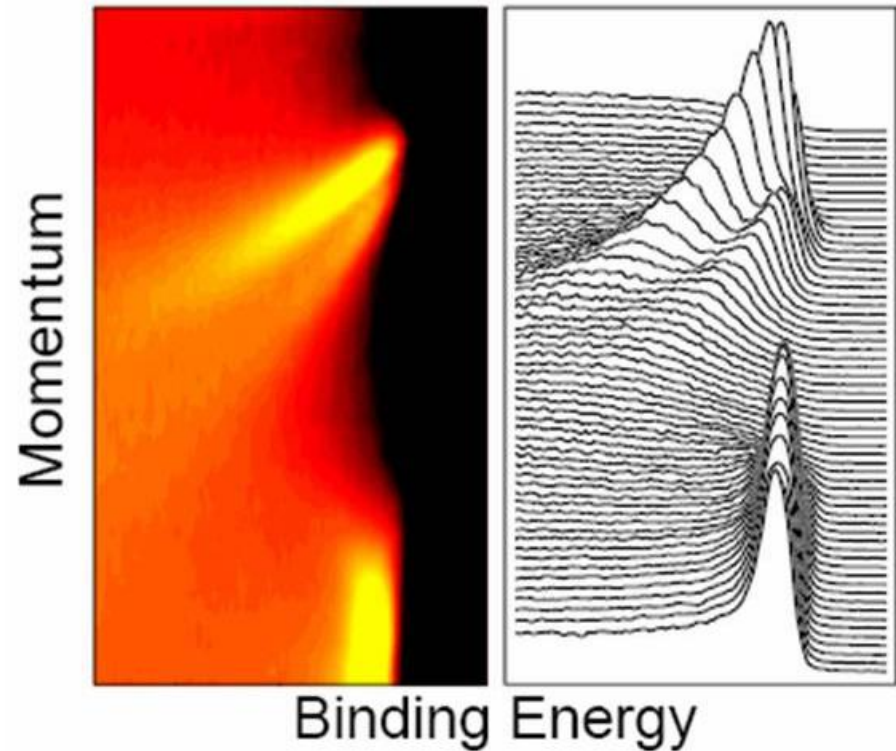
现代的能量分析器的发明者



Bjorn Wannberg

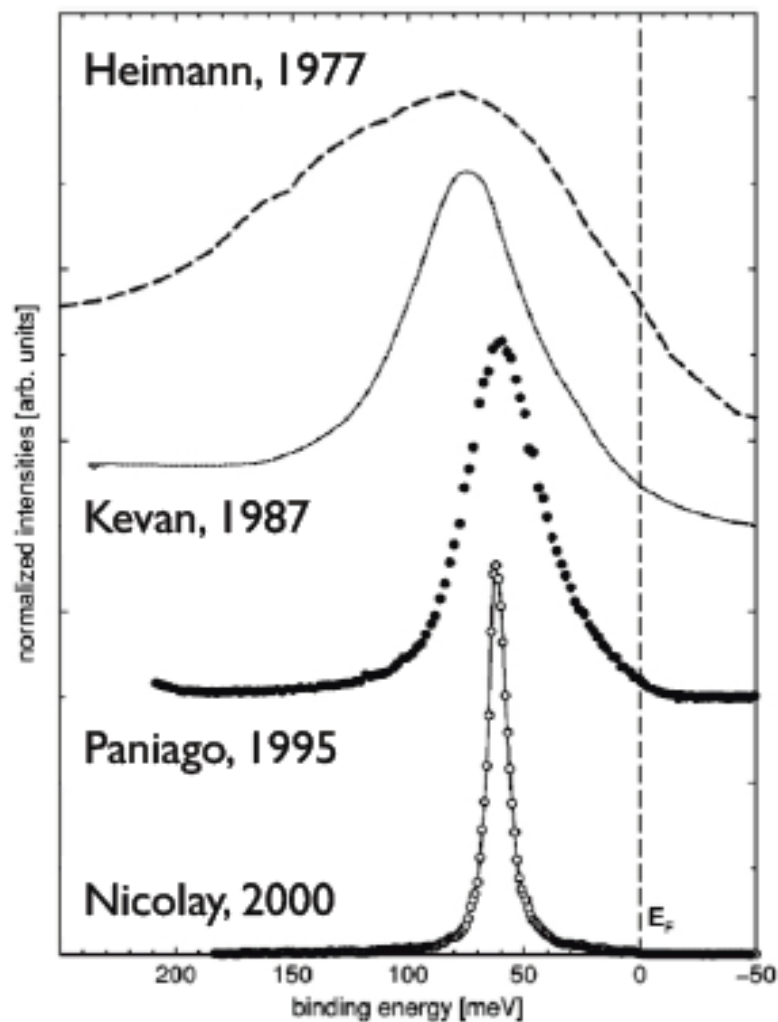
2008 APS

Keithley Award

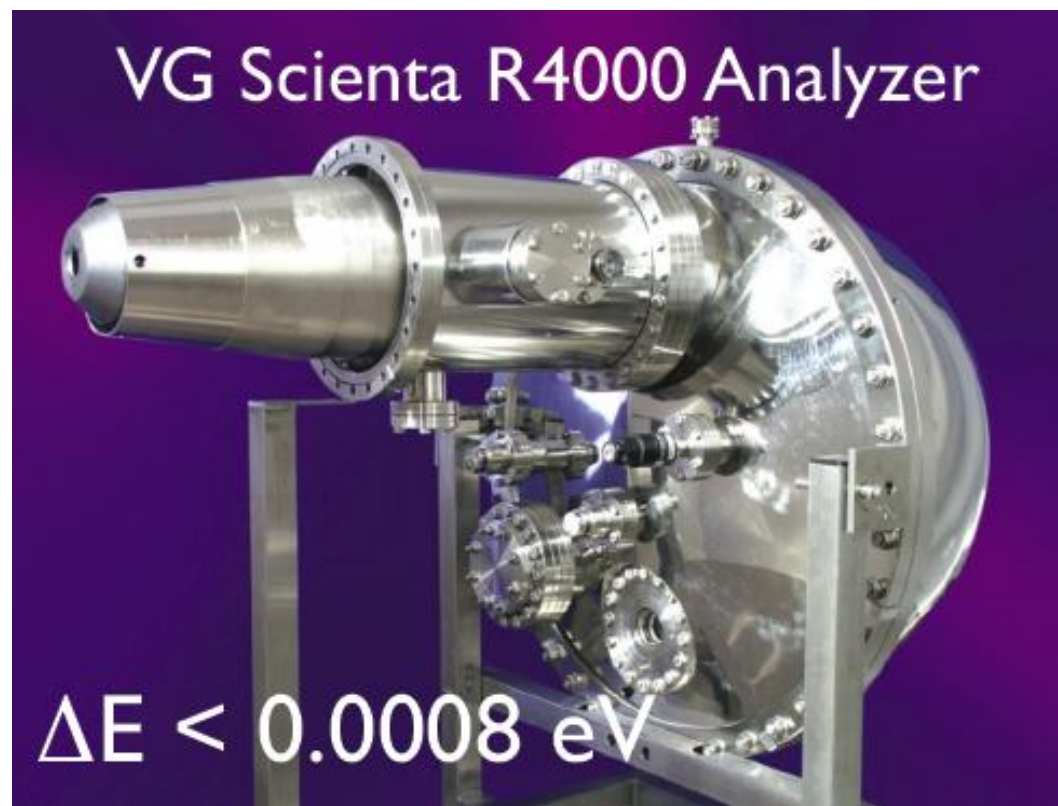


能量分辨率1meV, 提高20倍
角分辨率0.2度, 提高10倍
采集效率极大地提高

能量分析器

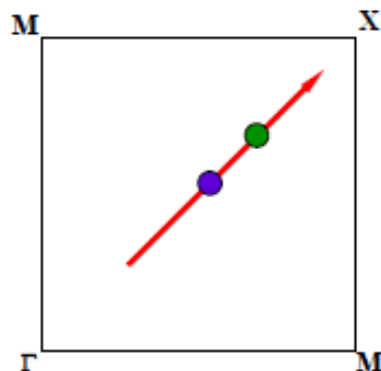


F. Reinert et al., PRB (2001)

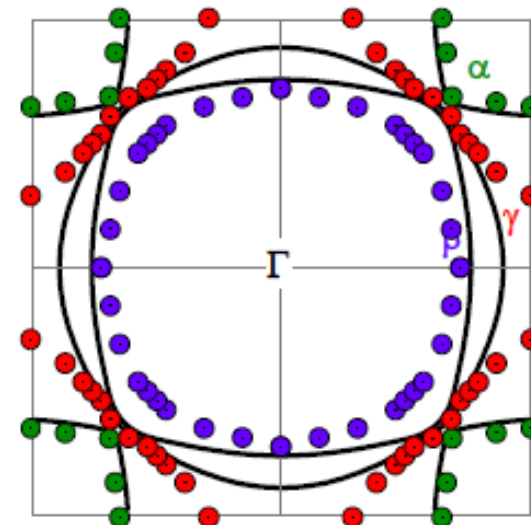
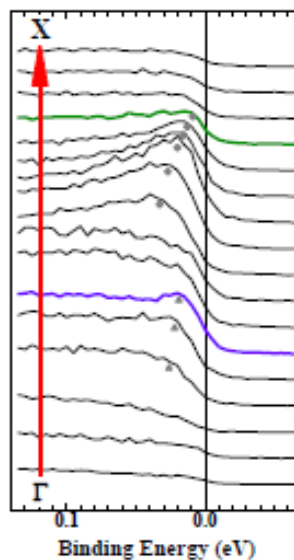


过去与现在

ARPES : circa 1996

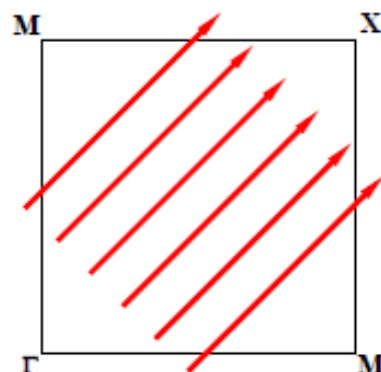


D.H. Lu *et al.*, PRL **76**, 4845 (1996)

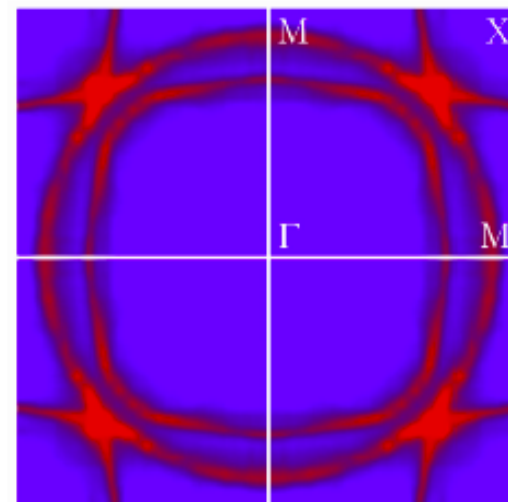
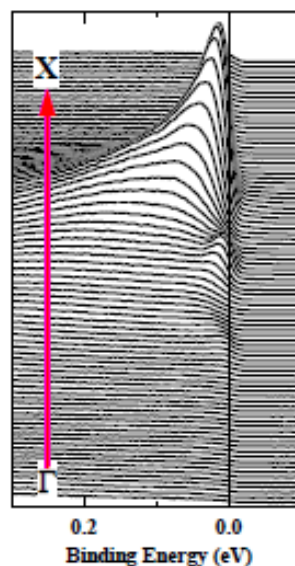


D.J. Singh, PRB **52**, 1358 (1995)

ARPES : present day



A. Damascelli *et al.*, PRL **85**, 5194 (2000)



**W[110]
Surface**

$k_{\parallel}$ -plane

electron
binding
energy

$k_{\parallel}$

$\bar{H}$

$\bar{S}$

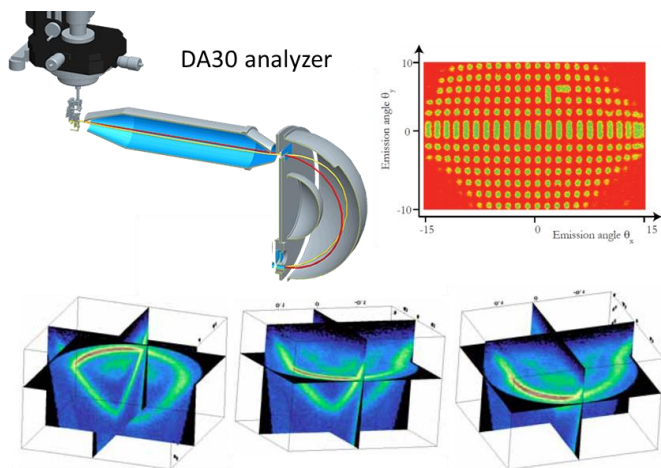
$\bar{N}$

$\bar{S}$

$\bar{G}$

$\bar{S}$

新一代高效率能量分析器



- Energy Resolution: better than 2meV
- Angular Resolution: 0.1°
- Angular Acceptance: 2D ± 15°
- Deflection mode: ± 15°

新型分析器

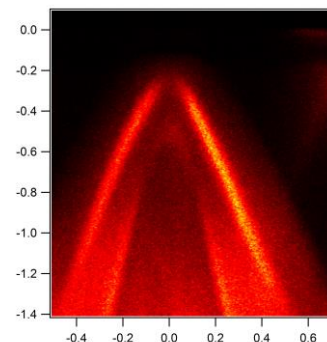
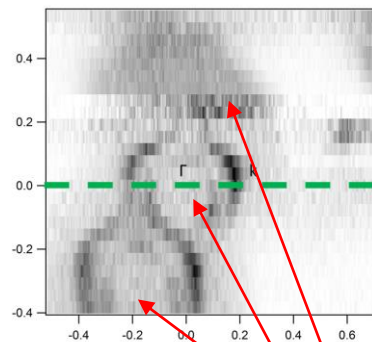
Scienta Omicron: DA30L

Specs: Phoibos 150 SAL

MBS: A-1 lens-4

R4000分析器

TiSe₂

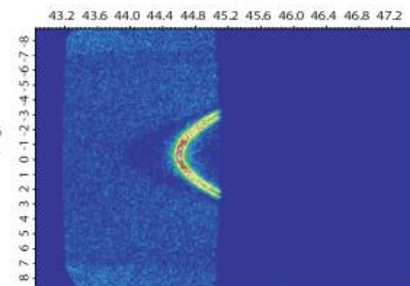
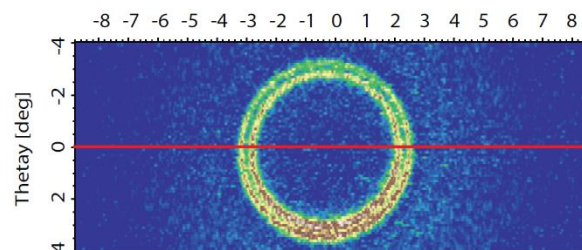


数据来自样品上不同区域，无法保证可靠性

DA30L分析器

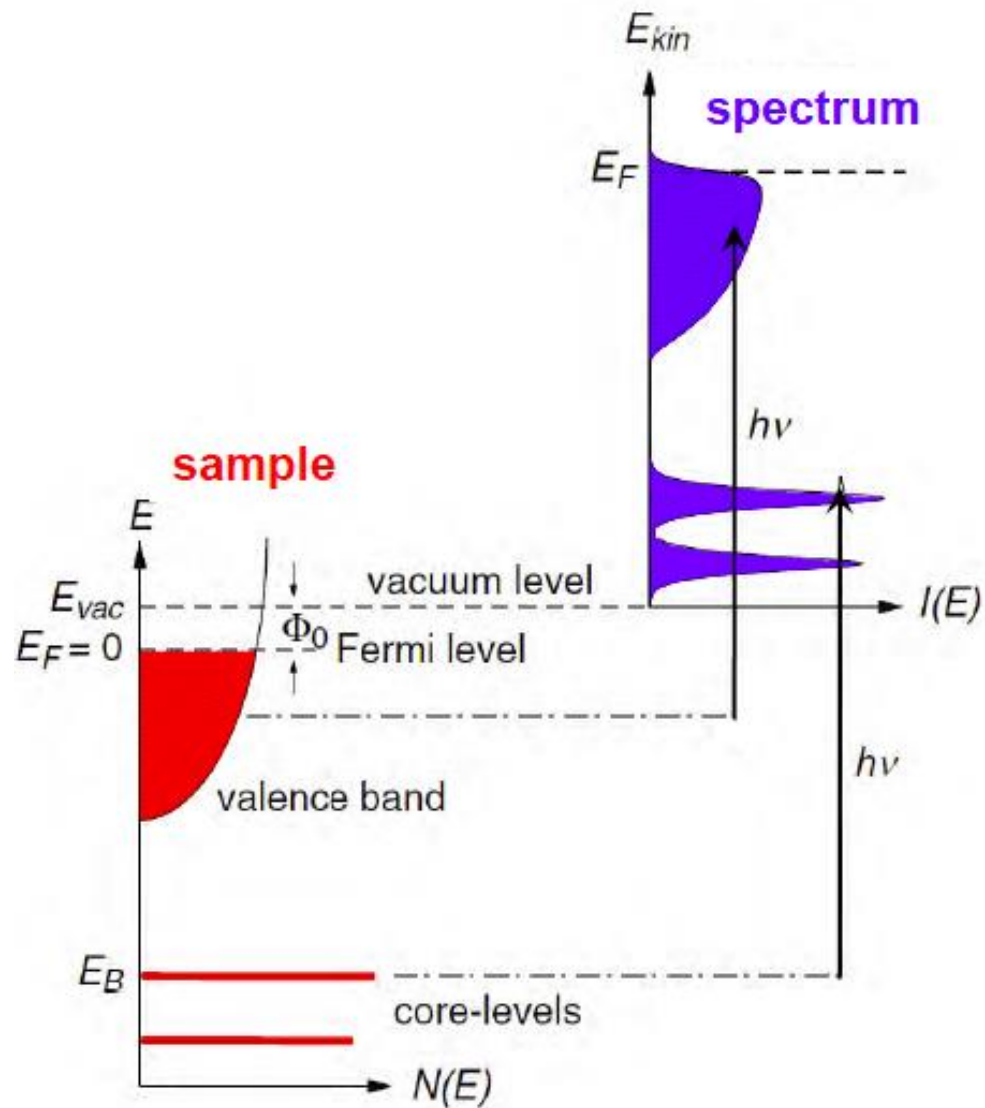
Au(111)表面态

采集时间 < 1 min



光电子过程

光电激发



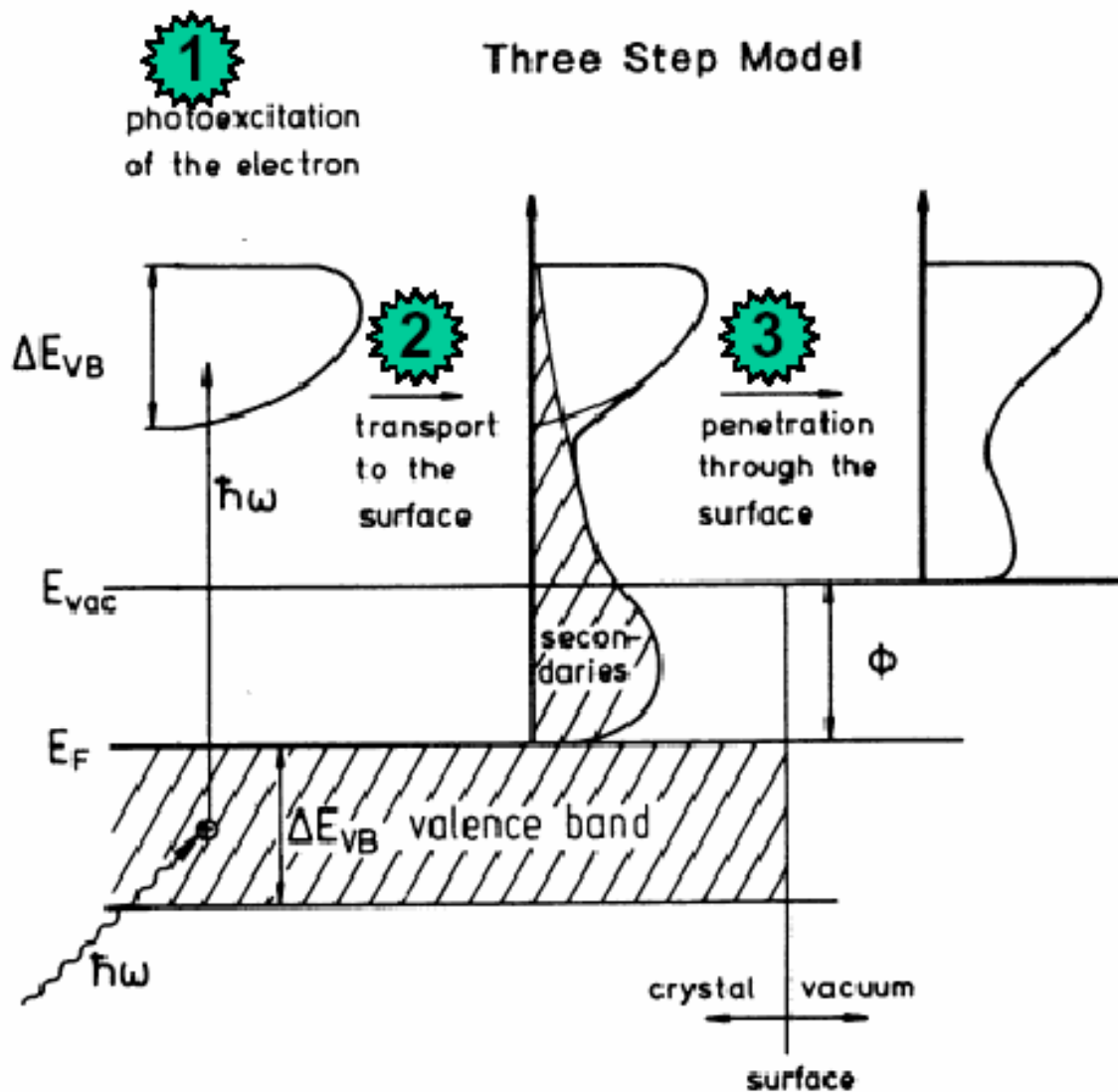
光电激发的三步模型

第一步：单个电子的**光激发**。

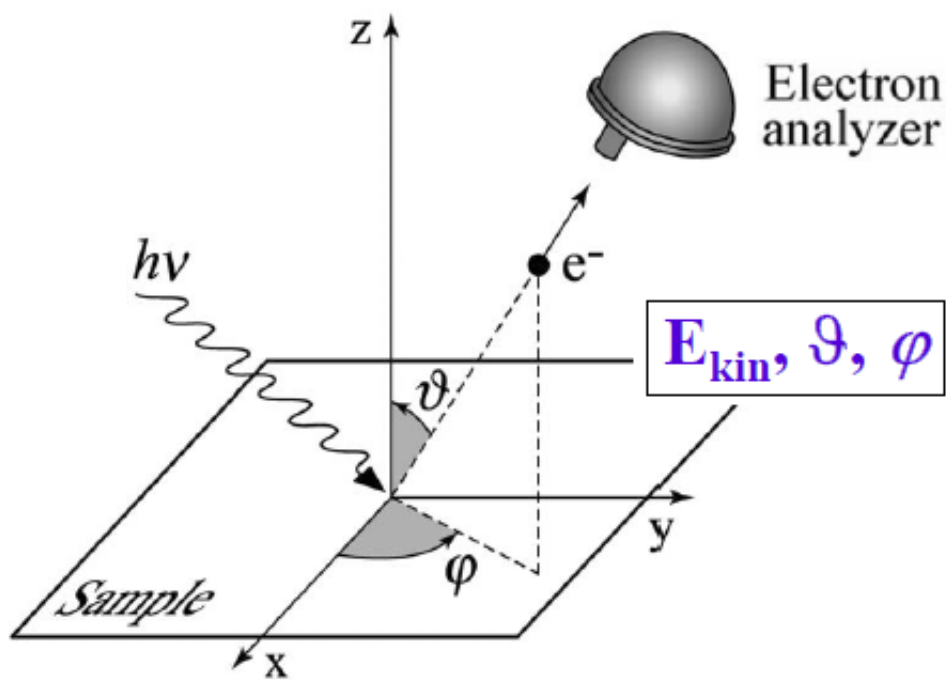
第二步：被激发的电子在固体中**传输到表面**，在此过程中，电子可能会受到非弹性散射。

第三步：具有足够动能的电子越过表面势垒，**发射**到真空中去。

光电激发的三步模型



基本公式



$$\mathbf{K} = \mathbf{p} / \hbar = \sqrt{2mE_{kin}} / \hbar$$

$$K_x = \frac{1}{\hbar} \sqrt{2mE_{kin}} \sin \vartheta \cos \varphi$$

$$K_y = \frac{1}{\hbar} \sqrt{2mE_{kin}} \sin \vartheta \sin \varphi$$

$$K_z = \frac{1}{\hbar} \sqrt{2mE_{kin}} \cos \vartheta$$

Vacuum

$$\begin{matrix} E_{kin} \\ \mathbf{K} \end{matrix}$$

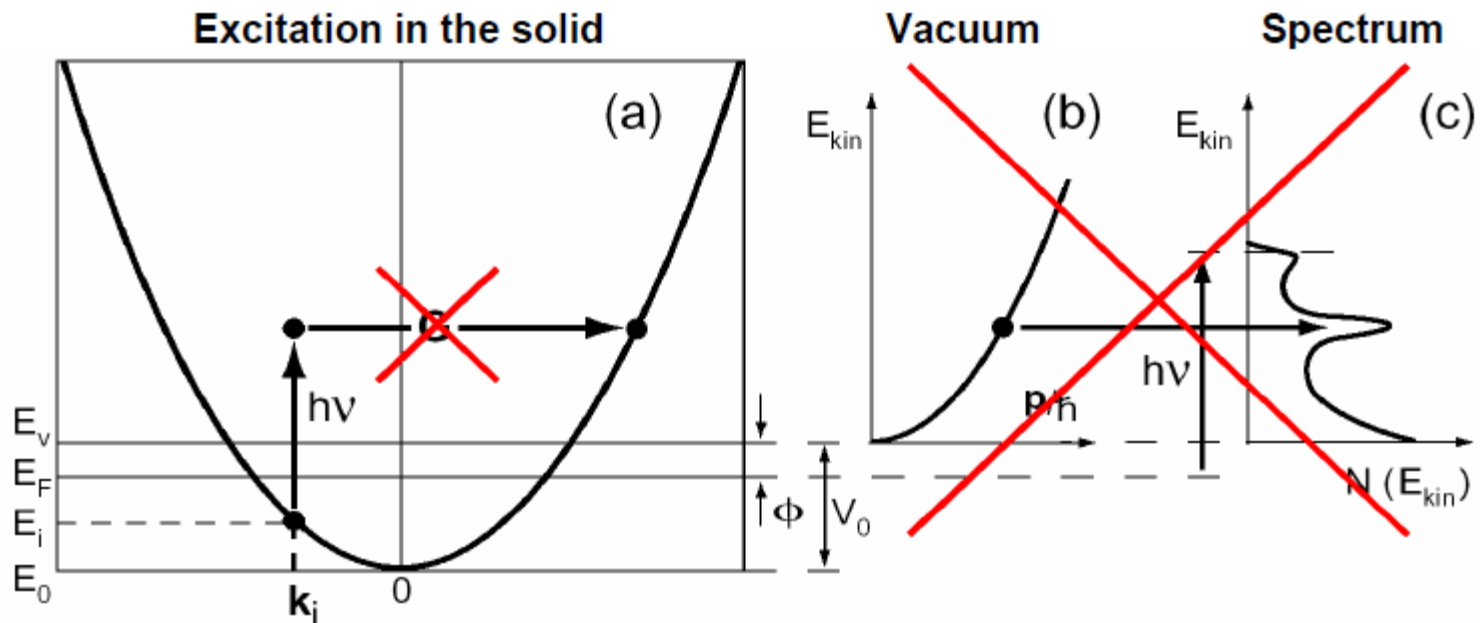
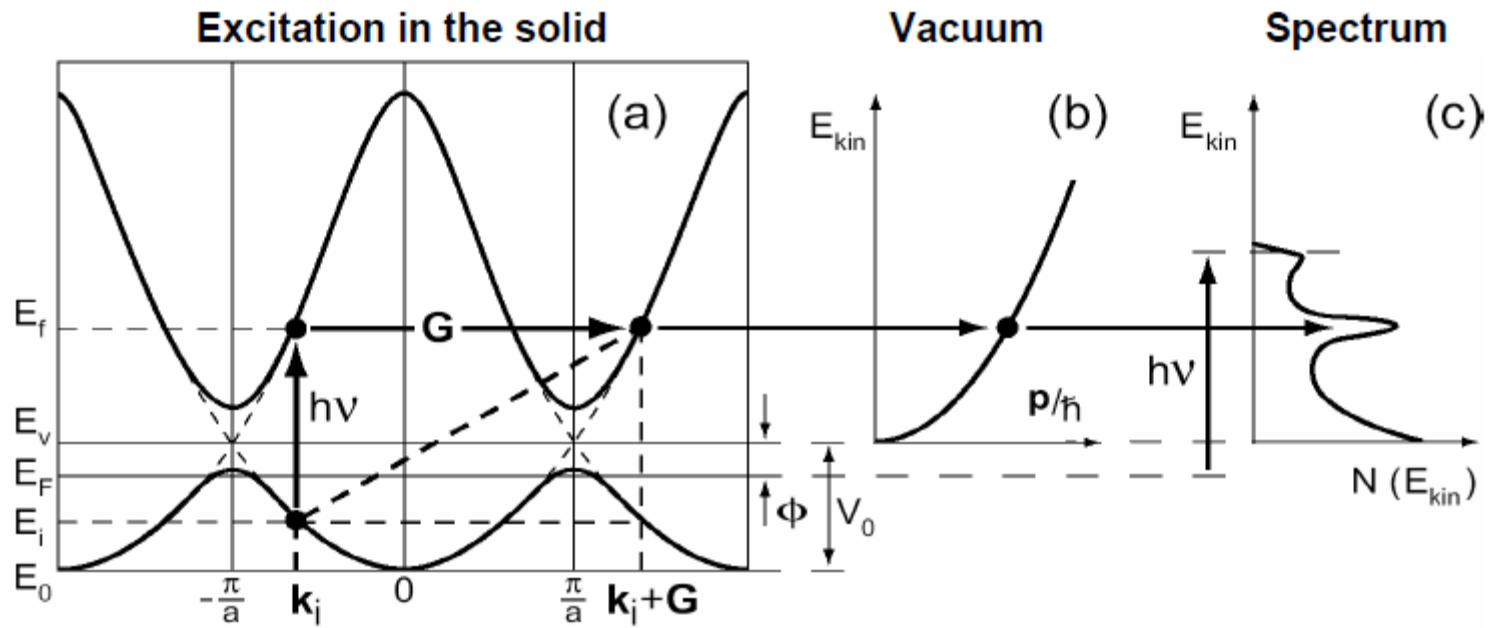
Conservation laws

$$\begin{aligned} E_f - E_i &= h\nu \\ \mathbf{k}_f - \mathbf{k}_i &= \cancel{\mathbf{k}_{h\nu}} \end{aligned}$$

Solid

$$\begin{matrix} E_B \\ \mathbf{k} \end{matrix}$$

Direct transition

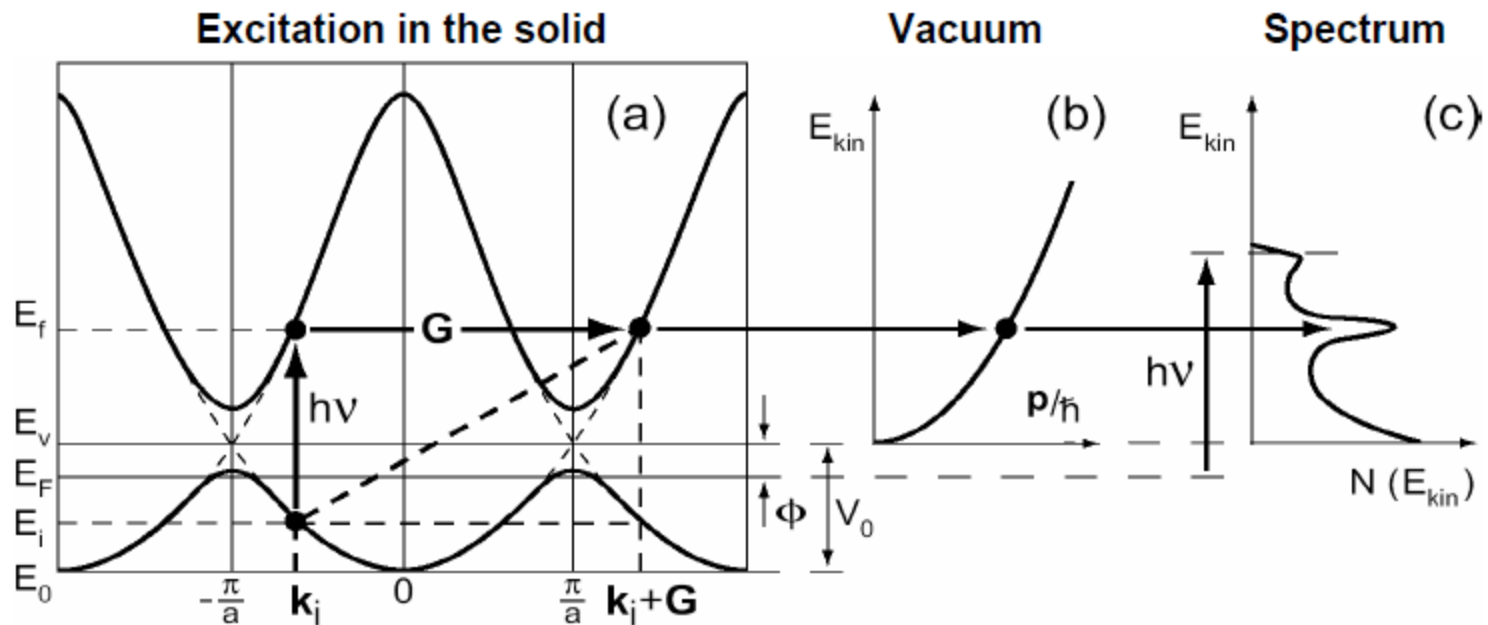


Inner potential and determination of k_z

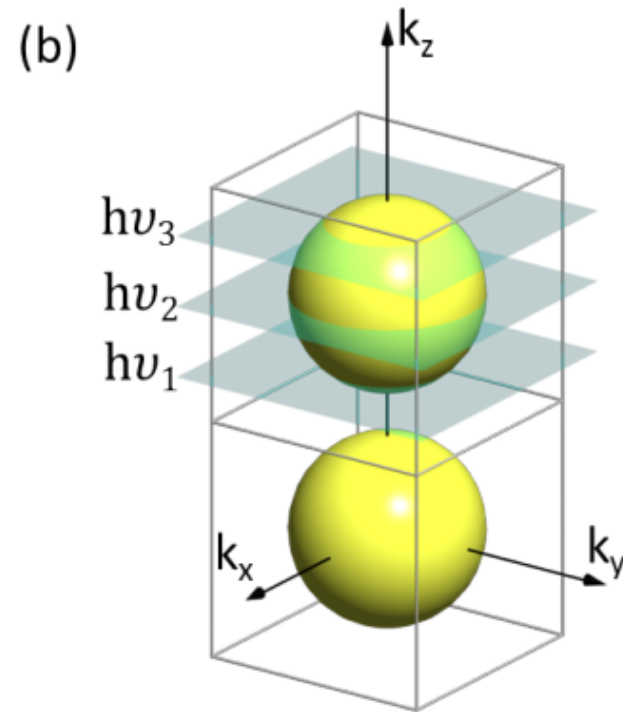
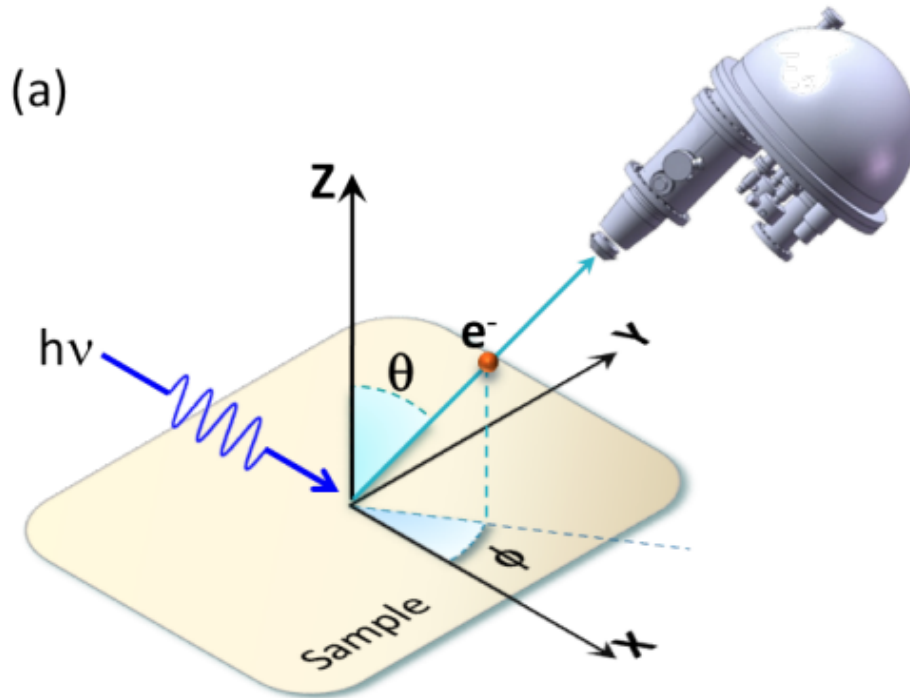
Free-electron final state $E_f(\mathbf{k}) = \frac{\hbar^2 \mathbf{k}^2}{2m} - |E_0| = \frac{\hbar^2 (\mathbf{k}_{\parallel}^2 + \mathbf{k}_{\perp}^2)}{2m} - |E_0|$

because $\frac{\hbar^2 \mathbf{k}_{\parallel}^2}{2m} = E_{kin} \sin^2 \vartheta$ $E_f = E_{kin} + \phi$ $V_0 = |E_0| + \phi$

→
$$\mathbf{k}_{\perp} = \frac{1}{\hbar} \sqrt{2m(E_{kin} \cos^2 \vartheta + V_0)}$$



Inner potential and determination of k_z



(c) $E_k = h\nu - w - E_B$

In vacuum:

$$k_x^V = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \cos(\phi)$$

$$k_y^V = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \sin(\phi)$$

$$k_z^V = \frac{\sqrt{2m_e E_k}}{\hbar} \cos(\theta)$$

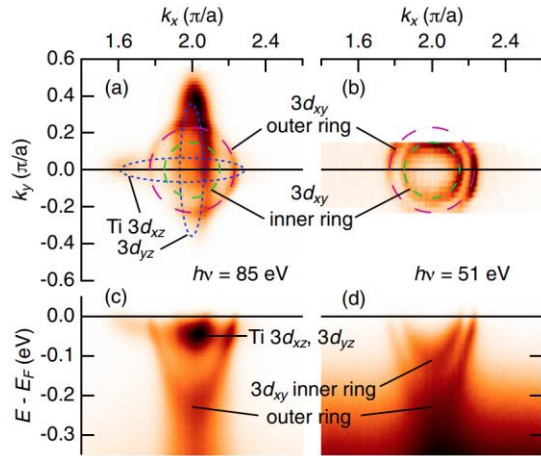
In crystal:

$$k_x = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \cos(\phi) = k_x^V$$

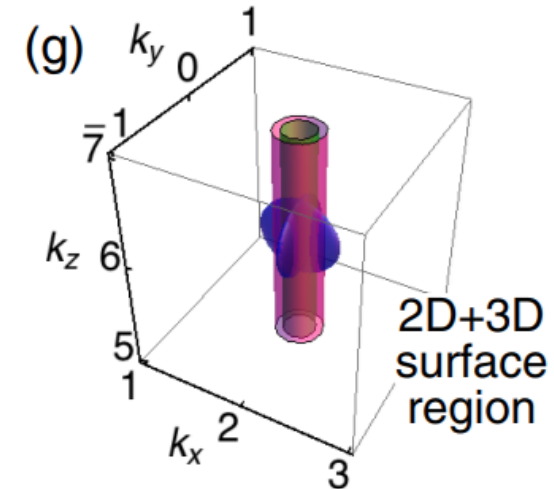
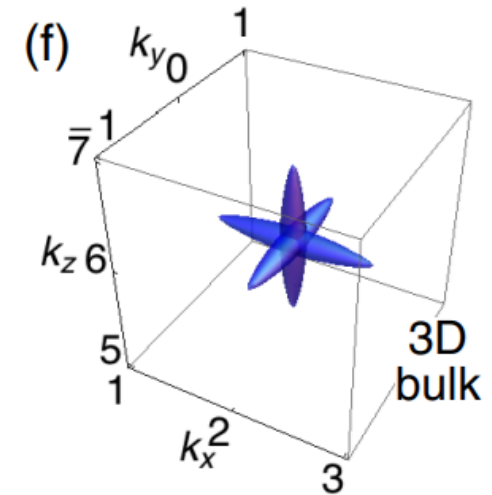
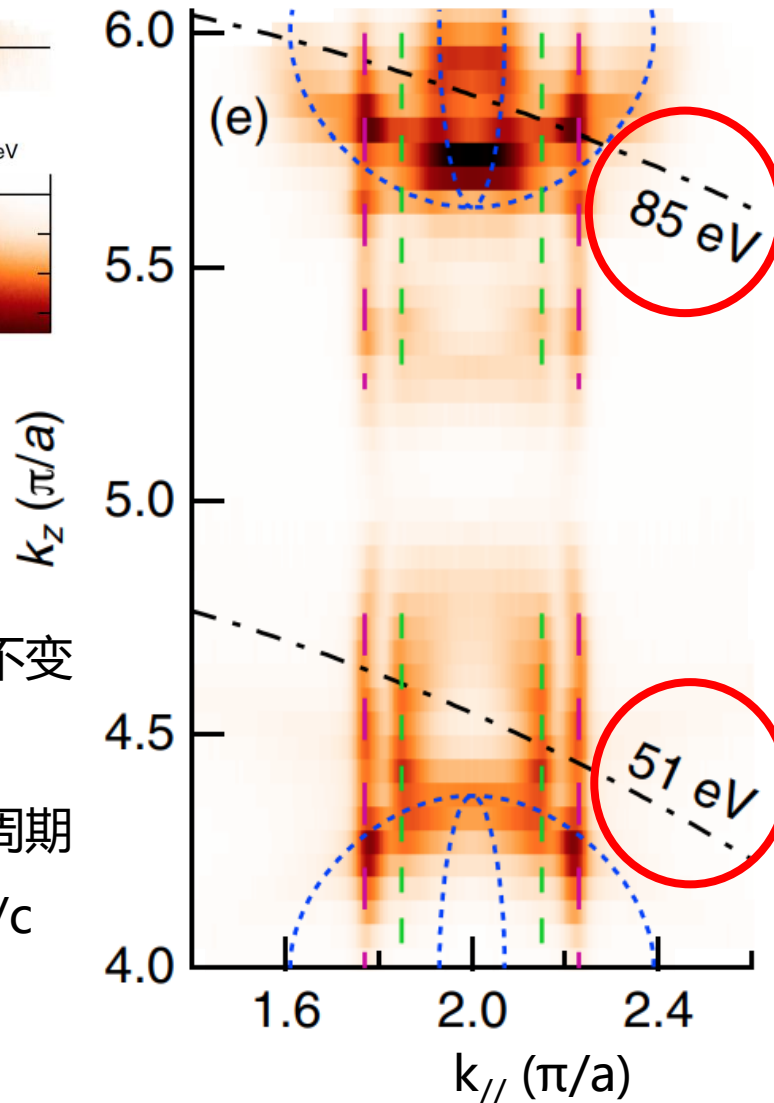
$$k_y = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \sin(\phi) = k_y^V$$

$$k_z = \sqrt{\frac{2m_e^*}{\hbar^2} (E_k + V_0) - \frac{2m_e E_k}{\hbar^2} \sin^2 \theta} \neq k_z^V$$

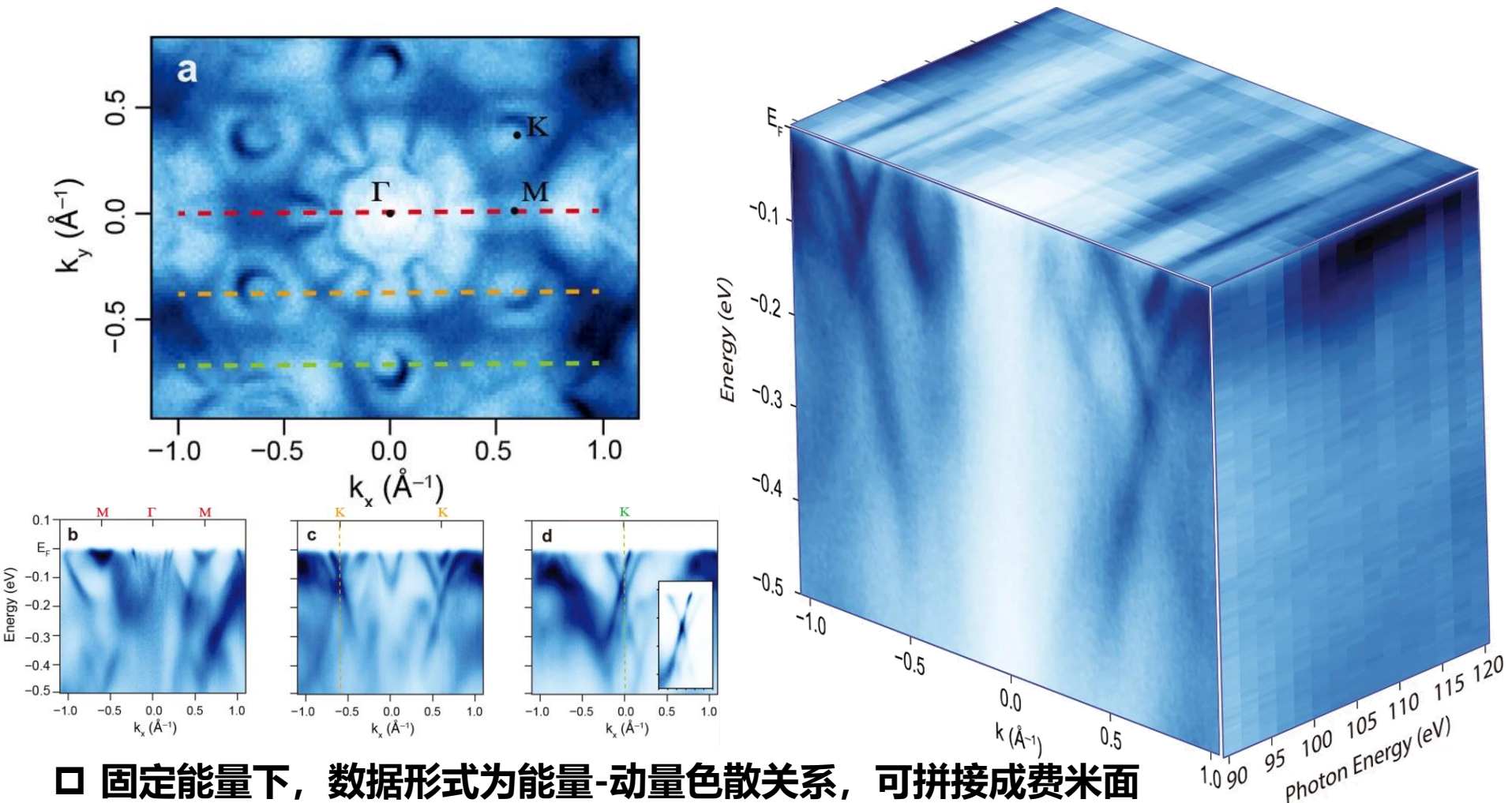
Inner potential and determination of k_z



- ❑ 二维电子态 k_z 色散不变 (无 k_z 色散)
- ❑ 三维电子态 k_z 色散周期性变化, 周期为 $2\pi/c$



Photon-energy dependence of ARPES



Nature 555, 638 (2018)

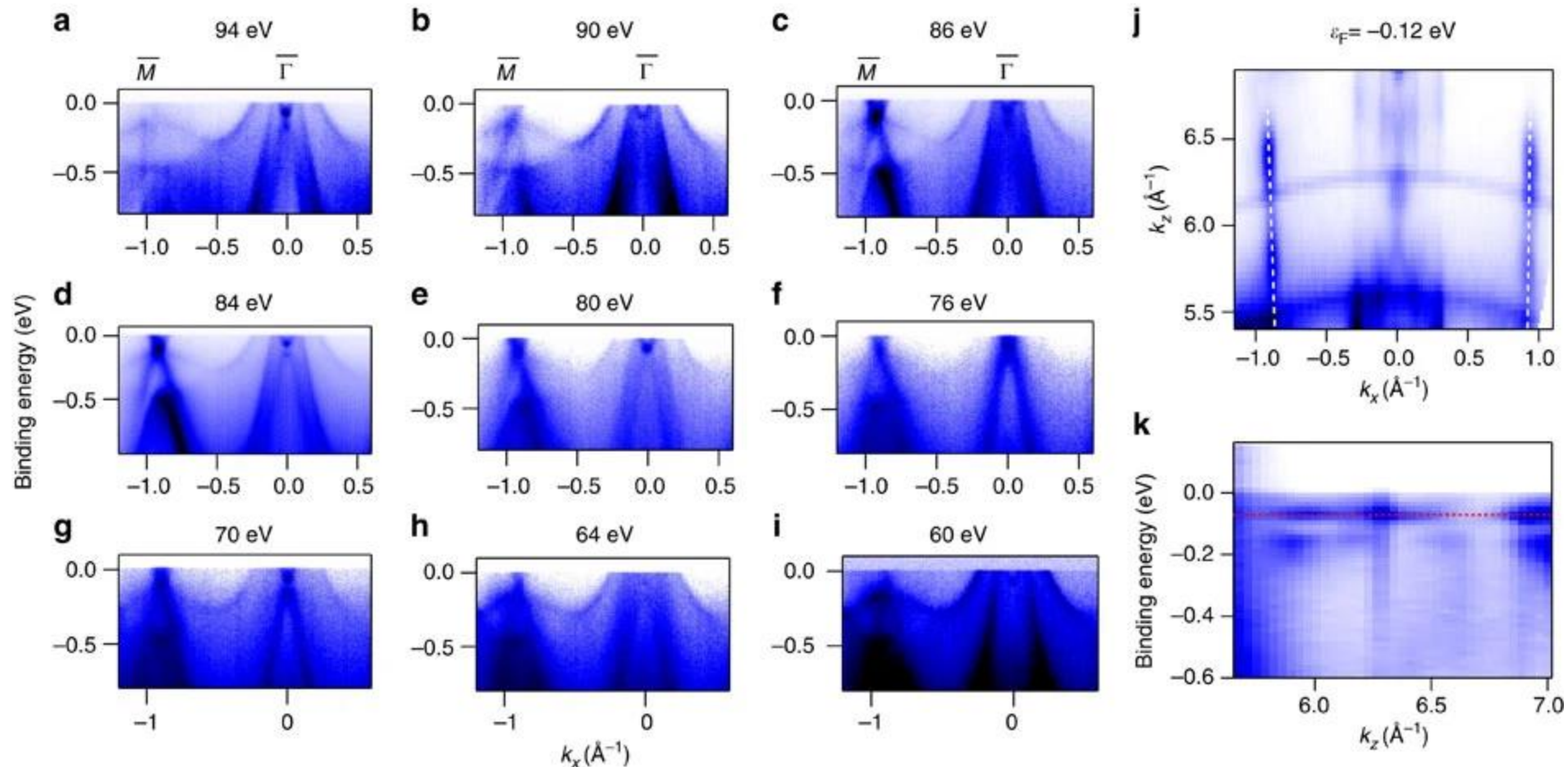
□ 固定能量下，数据形式为能量-动量色散关系，可拼接成费米面

- 如上面小图中，每一幅图展示固定 k_y 时沿着 k_x 方向的色散

□ 确定 Γ 点后，改变光子能量，在高对称方向采集数据，如右图所示

- 通过 k_F 随能量的变化，可以看到沿着 k_z 方向的规律，帮助判断电子态的维度

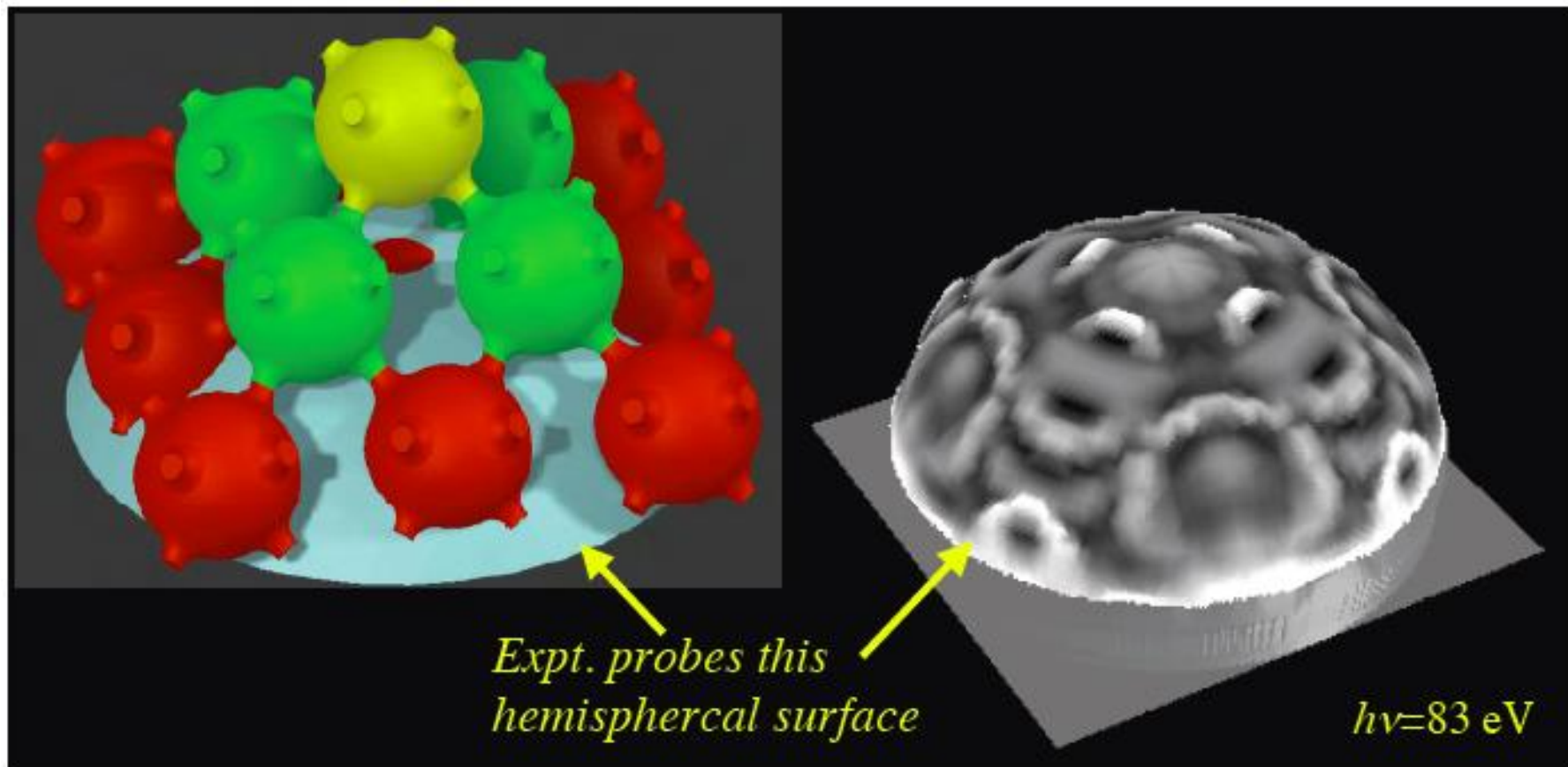
Photon-energy dependence of ARPES



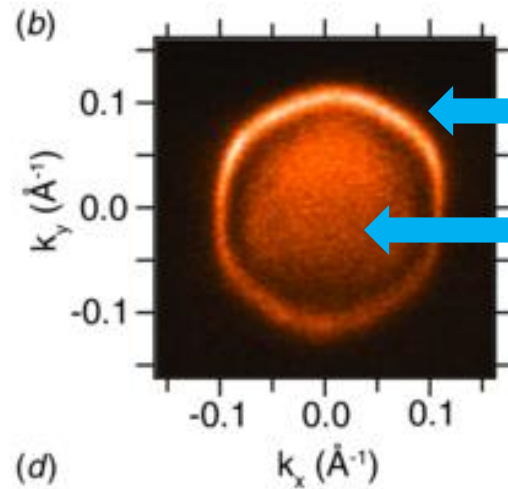
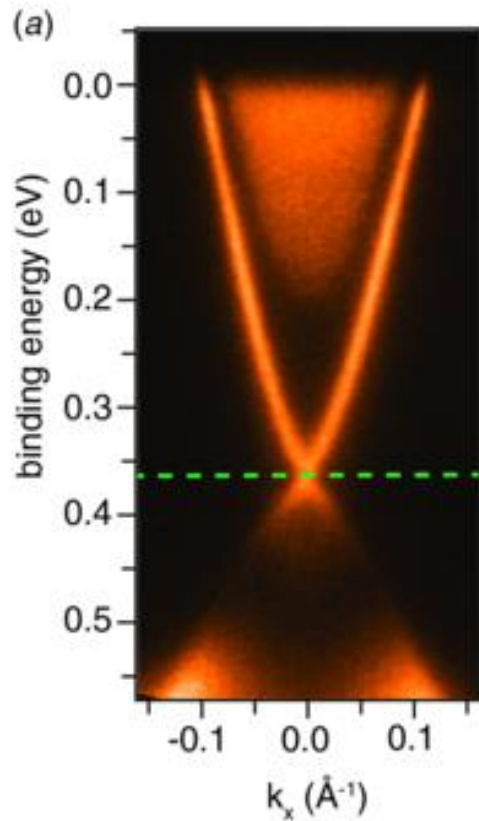
等动量面

model

data

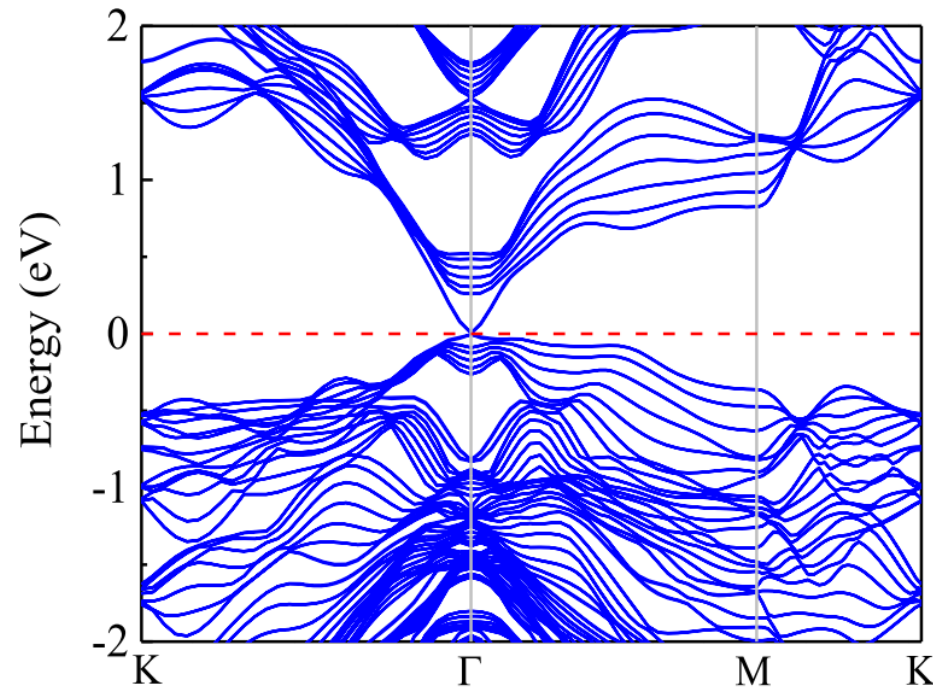


三维体态与二维表面态的展宽



表面态

体态



Angle-resolved photoemission, valence-band dispersions $E(\vec{k})$, and electron and hole lifetimes for GaAs

T.-C. Chiang, J. A. Knapp,* M. Aono,[†] and D. E. Eastman
 IBM Thomas J. Watson Research Center, Yorktown Heights, New York 10598
 (Received 3 December 1979)

$$E_f(\vec{k}) = \hbar^2 |\vec{k}|^2 / 2m + E_0 = \hbar^2 (k_{\parallel}^2 + k_{\perp}^2) / 2m + E_0 \quad \text{Final Bloch states.}$$

$$E_f(\vec{k}) = E_i(\vec{k}) + h\nu$$

$$E_f = E_k + e\Phi$$

$$\hbar k_{\parallel} = (2mE_k)^{1/2} \sin\theta$$

$$= [2m(E_i + h\nu - e\Phi)]^{1/2} \sin\theta$$

$$\hbar k_{\perp} = [2m(E_k \cos^2\theta - V_0)]^{1/2}$$

$$= \{2m[(E_i + h\nu - e\Phi) \cos^2\theta - V_0]\}^{1/2}$$

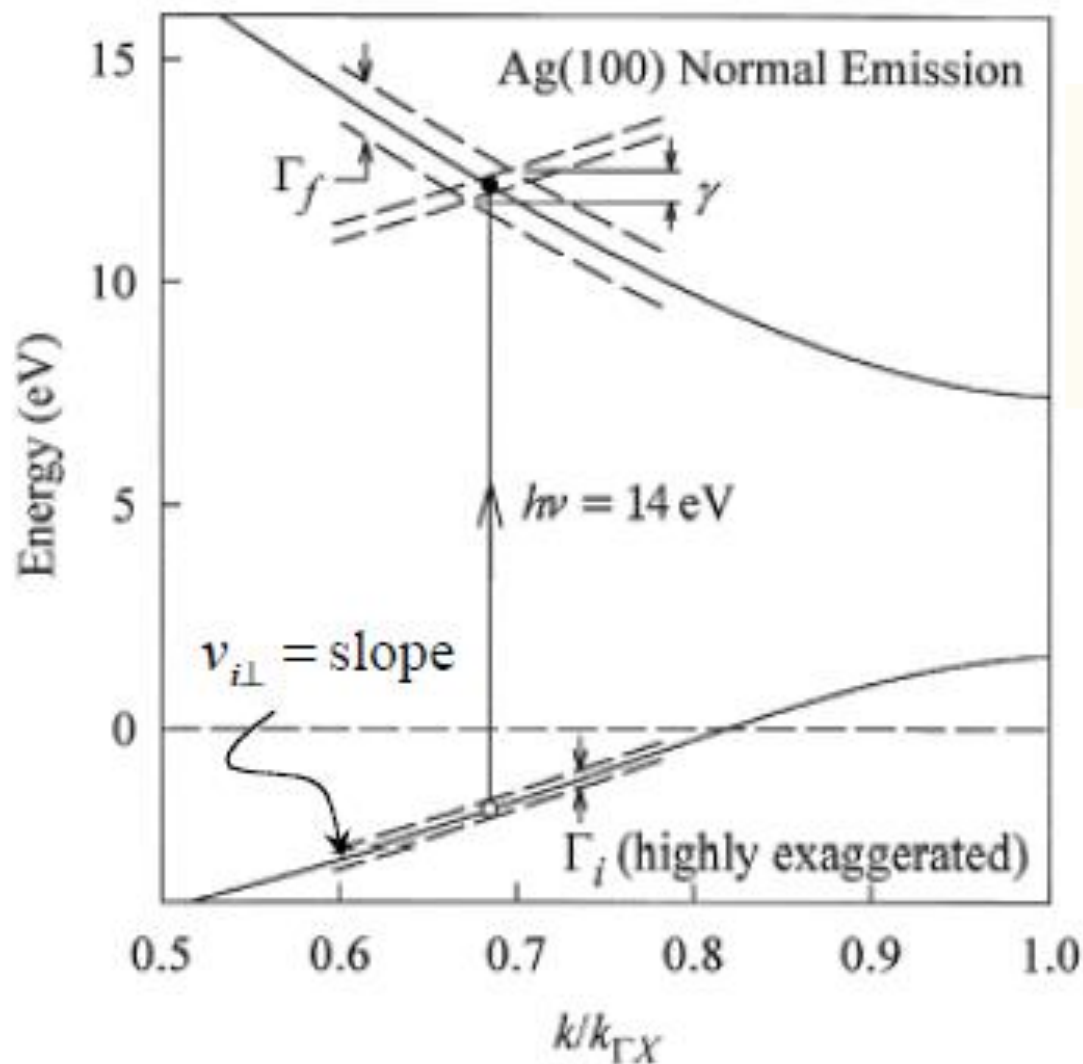
E_0 = "bottom of Muffin tin" –
 starting point for parabolic band
 dispersions = -9.34 eV for GaAs.

Direct or k-conserving transitions.
 $e\phi$ = work function of sample,
 E_k = kinetic energy

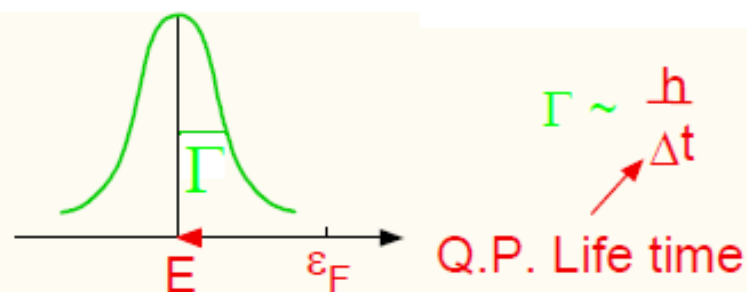
$V_0 = E_0 - e\phi$ = "Inner potential".
 Usually just a fitting parameter.

Normal emission: $\theta = 0$ $\hbar k_{\parallel} = 0$ $\hbar k_{\perp} = [2m(E_i + e\Phi - E_0)]^{1/2}$

谱线宽度



Interpretation of Line Widths



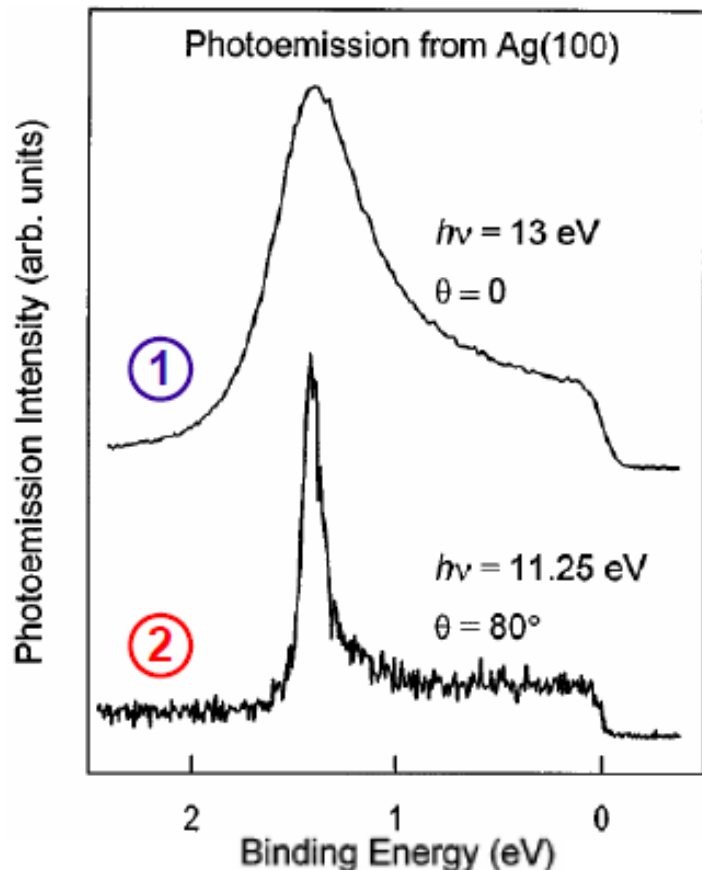
$$\gamma = \frac{\frac{\Gamma_i}{|v_{i\perp}|} + \frac{\Gamma_f}{|v_{f\perp}|}}{\left| \frac{1}{v_{i\perp}} - \frac{1}{v_{f\perp}} \right|}$$

正出射

谱线宽度

$$\left. \begin{array}{l} \text{FWHM of an} \\ \text{ARPES peak} \end{array} \right\} \Gamma = \frac{\frac{\Gamma_i}{|v_{i\perp}|} + \frac{\Gamma_f}{|v_{f\perp}|}}{\left| \frac{1}{v_{i\perp}} \left[1 - \frac{mv_{i\parallel} \sin^2 \vartheta}{\hbar k_{\parallel}} \right] - \frac{1}{v_{f\perp}} \left[1 - \frac{mv_{f\parallel} \sin^2 \vartheta}{\hbar k_{\parallel}} \right] \right|}$$

Hansen *et al.*, PRL **80**, 1766 (1998)



① if $E_i \simeq E_F$

$$\rightarrow \Gamma_i \rightarrow 0 \rightarrow \boxed{\Gamma \propto \Gamma_f}$$

② if $|v_{i\perp}| \simeq 0$ 二维、准二维系统

$$\rightarrow \Gamma = \frac{\Gamma_i}{\left| 1 - \frac{mv_{i\parallel} \sin^2 \vartheta}{\hbar k_{\parallel}} \right|} \equiv C \Gamma_i$$

if $v_{i\parallel} < 0$, large; θ large; $k_{\parallel}$ small

$$\rightarrow C < 1, \text{ and } \boxed{\Gamma < \Gamma_i}$$